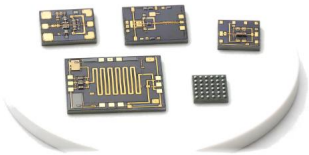
Product catalog

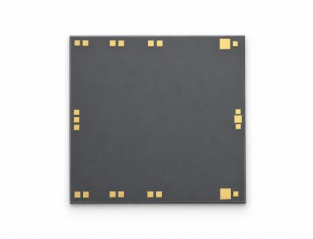
Bare Die and Chip-Scale RF Devices

Bare die and chip-scale RF devices remove package size and parasitics but transfer assembly, grounding, thermal and verification responsibility to the integrator. Compare die geometry, test grade, pad metallurgy, attach, interconnect and traceability.



Products: 244

Revision: 57 · Revision date: 2026-11-12



LCI-PA-11500-18000-PS44p5T

11500–18000 MHz GaN MMIC Power Amplifier Die

A GaN MMIC power amplifier die for 11.5–18 GHz microwave transmit stages. It supports continuous-wave and pulsed operation and integrates DC blocking in both RF signal paths.

Operating frequency: Symbol: f; Minimum: 11500; Maximum: 18000; Value: 11500–18000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 44; Typical: 44.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19; Typical: 19.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V; Pin = 25 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-14000-18000-PS42p5T

14000–18000 MHz GaN MMIC Power Amplifier Die

Saturated output power: 42 dBm (minimum) / 42.5 dBm (typical); Power gain: 22 dB (minimum) / 22.5 dB (typical); Power-added efficiency: 35 % (minimum). Die dimensions: 3 × 2 × 0.1 mm.

Operating frequency: Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

Saturated output power: Minimum: 42; Typical: 42.5; Unit: dBm

Power gain: Minimum: 22; Typical: 22.5; Unit: dB

Power-gain flatness: Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-14200-16800-PS48T

14200–16800 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 48 dBm (typical); Power gain: 20 dB (typical); PAE: 35 % (typical). Die dimensions: 3.6 × 5.9 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 14200; Maximum: 16800; Value: 14200–16800; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.35; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; Pin = 28 dBm; τ = 100 µs; D = 5%; pulsed

Product details Product datasheet



LCI-PA-14500-17200-PS48T

14500–17200 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 48 dBm (typical); Power gain: 20 dB (typical); PAE: 35 % (typical). Die dimensions: 3.6 × 5.9 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 14500; Maximum: 17200; Value: 14500–17200; Unit: MHz

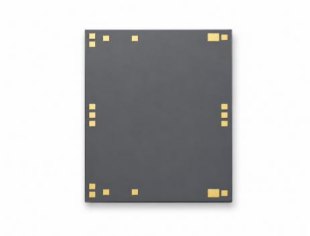
Saturated output power: Symbol: Psat; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.35; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 28 dBm; τ = 100 µs; D = 5%; pulsed

Product details Product datasheet



LCI-PA-13750-14500-PS45MIN

13750–14500 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 45 dBm (minimum); Power gain: 20 dB (minimum); PAE: 37 % (minimum) / 38 % (typical). Die dimensions: 2.8 × 3.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 13750; Maximum: 14500; Value: 13750–14500; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 45; Unit: dBm

Power gain: Symbol: Gp; Minimum: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -3.08 V; pulsed

Product details Product datasheet



LCI-PA-13750-15250-PS46T

13750–15250 MHz GaN MMIC Power Amplifier Die

Saturated output power: 46 dBm (typical); Power gain: 21 dB (typical); Power-added efficiency: 33 % (typical). Die dimensions: 5 × 6 × 0.08 mm.

Operating frequency: Minimum: 13750; Maximum: 15250; Value: 13750–15250; Unit: MHz

Saturated output power: Typical: 46; Unit: dBm

Power gain: Typical: 21; Unit: dB

Power-gain flatness: Maximum: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -3.05 V; CW

Product details Product datasheet



LCI-PA-8000-12000-PS48p5T

8000–12000 MHz GaN MMIC Power Amplifier Die

Saturated output power: 48 dBm (minimum) / 48.5 dBm (typical); Power gain: 23 dB (minimum) / 23.5 dB (typical); Power-added efficiency: 44 % (typical). Die dimensions: 4 × 5.8 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Saturated output power: Minimum: 48; Typical: 48.5; Unit: dBm

Power gain: Minimum: 23; Typical: 23.5; Unit: dB

Power-gain flatness: Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-13800-18200-PS47p5T

13800–18200 MHz GaN MMIC Power Amplifier Die

PSAT: 47 dBm (minimum) / 47.5 dBm (typical); Power gain: 21 dB (minimum) / 21.5 dB (typical); PAE: 33 % (typical). Die dimensions: 3.6 × 5.9 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 13800; Maximum: 18200; Value: 13800–18200; Unit: MHz

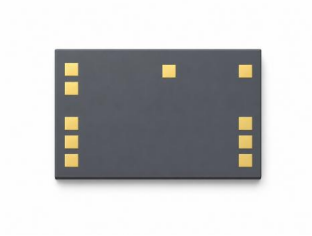
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21; Typical: 21.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-14000-18000-PS37p5T

14000–18000 MHz GaN MMIC Power Amplifier Die

PSAT: 37 dBm (minimum) / 37.5 dBm (typical); Power gain: 15 dB (minimum) / 15.5 dB (typical); PAE: 35 % (typical). Die dimensions: 1.5 × 1 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 37; Typical: 37.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 15; Typical: 15.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.4; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-12200-16000-PS46p5T

12200–16000 MHz GaN MMIC Power Amplifier Die

PSAT: 46 dBm (minimum) / 46.5 dBm (typical); Power gain: 19 dB (minimum) / 19.5 dB (typical); PAE: 33 % (typical). Die dimensions: 4.2 × 6.02 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 12200; Maximum: 16000; Value: 12200–16000; Unit: MHz

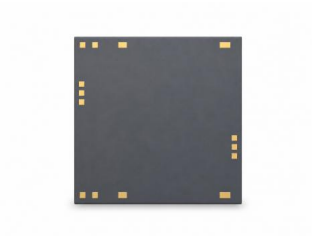
Saturated output power: Symbol: Psat; Minimum: 46; Typical: 46.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19; Typical: 19.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -3.0 V

Product details Product datasheet



LCI-PA-26000-40000-PS40p5T

26000–40000 MHz GaN MMIC Power Amplifier Die

Power gain: 15 dB (typical); PSAT: 40.5 dBm (typical); PAE: 23 % (typical). Die dimensions: 3.4 × 3.4 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 26000; Maximum: 40000; Value: 26000–40000; Unit: MHz

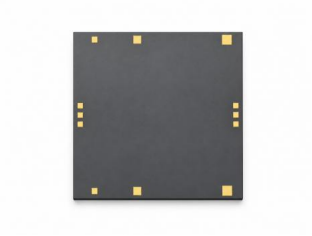
Small-signal gain: Symbol: S21; Typical: 22; Unit: dB

Power gain: Symbol: Gp; Typical: 15; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +22 V; Id = 0.8 A

Product details Product datasheet



LCI-PA-31000-37000-PS41T

31000–37000 MHz MMIC Power Amplifier Die

PSAT: 41 dBm (typical); PAE: 26 % (typical); Small-signal gain: 21 dB (typical). Die dimensions: 3.6 × 3.6 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 31000; Maximum: 37000; Value: 31000–37000; Unit: MHz

Small-signal gain: Symbol: S21; Typical: 21; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 41; Unit: dBm

TA = +25 °C; Vd = +22 V; Id = 1 A

Product details Product datasheet



LCI-PA-33000-37000-PS45T

33000–37000 MHz MMIC Power Amplifier Die

PSAT: 45 dBm (typical); PAE: 22 % (typical); Small-signal gain: 23 dB (typical). Die dimensions: 3.6 × 6.2 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 33000; Maximum: 37000; Value: 33000–37000; Unit: MHz

Small-signal gain: Symbol: S21; Typical: 23; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

TA = +25 °C; Vd = +28 V; Id = 2.1 A

Product details Product datasheet



LCI-PA-18000-40000-PS40p5T

18000–40000 MHz GaN MMIC Power Amplifier Die

PSAT: 40.5 dBm (typical); PAE: 15 % (typical); Small-signal gain: 21 dB (typical). Die dimensions: 3.4 × 4.2 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 18000; Maximum: 40000; Value: 18000–40000; Unit: MHz

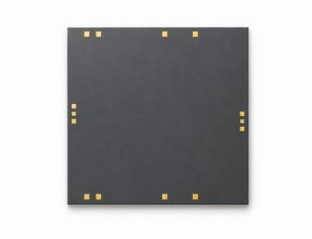
Small-signal gain: Symbol: S21; Typical: 21; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 40.5; Unit: dBm

TA = +25 °C; Vd = +18 V; Id = 2.2 A

Product details Product datasheet



LCI-PA-92000-96000-PS36T

92000–96000 MHz MMIC Power Amplifier Die

PSAT: 36 dBm (typical); PAE: 9 % (typical); Small-signal gain: 19 dB (typical). Die dimensions: 5.1 × 5.1 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 92000; Maximum: 96000; Value: 92000–96000; Unit: MHz

Small-signal gain: Symbol: S21; Typical: 19; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 36; Unit: dBm

TA = +25 °C; Vd = +18 V; Id = 1.2 A

Product details Product datasheet



LCI-PA-27000-31000-PS43T

27000–31000 MHz Power Amplifier Die

PSAT: 43 dBm (typical); PAE: 28 % (typical); Small-signal gain: 23 dB (typical). Die dimensions: 3.26 × 4.8 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 27000; Maximum: 31000; Value: 27000–31000; Unit: MHz

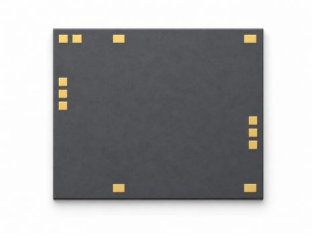
Small-signal gain: Symbol: S21; Typical: 23; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±0.5; Unit: dB

Saturated output power: Symbol: Psat; Typical: 43; Unit: dBm

TA = +25 °C; Vd = +22 V; Id = 0.9 A

Product details Product datasheet



LCI-PA-50000-63000-PS37T

50000–63000 MHz GaN MMIC Power Amplifier Die

PSAT: 37 dBm (typical); PAE: 20 % (typical); Small-signal gain: 18 dB (typical). Die dimensions: 2.9 × 2.4 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 50000; Maximum: 63000; Value: 50000–63000; Unit: MHz

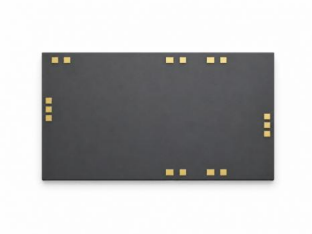
Small-signal gain: Symbol: S21; Typical: 18; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1.5; Unit: dB

Saturated output power: Symbol: Psat; Typical: 37; Unit: dBm

TA = +25 °C; Vd = +18 V; Id = 0.77 A

Product details Product datasheet



LCI-PA-92000-96000-PS34T

92000–96000 MHz MMIC Power Amplifier Die

PSAT: 34 dBm (typical); PAE: 10 % (typical); Small-signal gain: 19 dB (typical). Die dimensions: 4.5 × 2.6 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 92000; Maximum: 96000; Value: 92000–96000; Unit: MHz

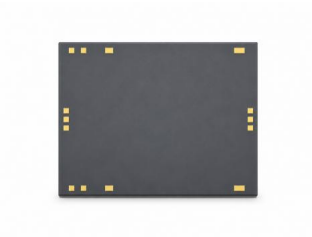
Small-signal gain: Symbol: S21; Typical: 19; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 34; Unit: dBm

TA = +25 °C; Vd = +18 V; Id = 1.2 A

Product details Product datasheet



LCI-PA-18000-26500-PS41T

18000–26500 MHz GaN MMIC Power Amplifier Die

PSAT: 41 dBm (typical); PAE: 26 % (typical); Power gain: 19 dB (typical). Die dimensions: 4.1 × 3.2 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 18000; Maximum: 26500; Value: 18000–26500; Unit: MHz

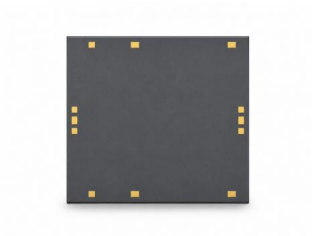
Small-signal gain: Symbol: S21; Typical: 25; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±0.4; Unit: dB

Saturated output power: Symbol: Psat; Typical: 41; Unit: dBm

TA = +25 °C; Vd = +22 V; Id = 0.9 A

Product details Product datasheet



LCI-PA-27000-31000-PS42T

27000–31000 MHz GaN MMIC Power Amplifier Die

PSAT: 42 dBm (typical); PAE: 30 % (typical); Small-signal gain: 23 dB (typical). Die dimensions: 3.26 × 3 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 27000; Maximum: 31000; Value: 27000–31000; Unit: MHz

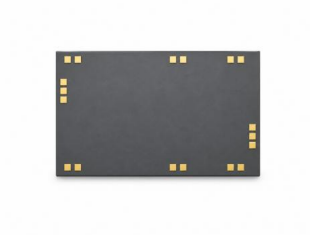
Small-signal gain: Symbol: S21; Typical: 23; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.5; Unit: dB

Saturated output power: Symbol: Psat; Typical: 42; Unit: dBm

TA = +25 °C; Vd = +22 V; Id = 0.5 A

Product details Product datasheet



LCI-PA-15000-43000-PS30T

15000–43000 MHz Power Amplifier Die

PSAT: 30 dBm (typical); PAE: 18 % (typical); Small-signal gain: 18 dB (minimum) / 20 dB (typical) / 22 dB (maximum). Die dimensions: 3.94 × 2.48 × 0.07 mm.

Operating frequency: Symbol: f; Minimum: 15000; Maximum: 43000; Value: 15000–43000; Unit: MHz

Small-signal gain: Symbol: S21; Minimum: 18; Typical: 20; Maximum: 22; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±2; Unit: dB

Output power at 1 dB compression: Typical: 29.5; Unit: dBm

TA = +25 °C; Vd = +5 V; Id = 0.9 A

Product details Product datasheet



LCI-PA-92000-96000-PS26p5T

92000–96000 MHz Power Amplifier Die

PSAT: 26.5 dBm (typical); PAE: 12 % (typical) / 13 % (maximum); Small-signal gain: 18 dB (typical). Die dimensions: 3.25 × 1.15 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 92000; Maximum: 96000; Value: 92000–96000; Unit: MHz

Small-signal gain: Symbol: S21; Typical: 18; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±0.5; Unit: dB

Saturated output power: Symbol: Psat; Typical: 26.5; Unit: dBm

TA = +25 °C; Vd = +18 V; Id = 0.11 A

Product details Product datasheet



LCI-PA-15000-17000-PS45T-PG21T

15000–17000 MHz GaN MMIC Power Amplifier Die

PSAT: 45 dBm (typical); Power gain: 21 dB (typical); PAE: 37 % (typical). Die dimensions: 3.45 × 3.95 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 15000; Maximum: 17000; Value: 15000–17000; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-12700-14500-PS47T

12700–14500 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 46.8 dBm (minimum) / 47 dBm (typical); Power gain: 18.8 dB (minimum) / 19 dB (typical); PAE: 37 % (typical). Die dimensions: 3.7 × 5.9 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 12700; Maximum: 14500; Value: 12700–14500; Unit: MHz

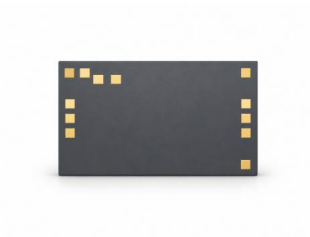
Saturated output power: Symbol: Psat; Minimum: 46.8; Typical: 47; Unit: dBm

Power gain: Symbol: Gp; Minimum: 18.8; Typical: 19; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.96 V; pulsed

Product details Product datasheet



LCI-PA-15000-18000-PS38T

15000–18000 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 38 dBm (typical); Power gain: 20 dB (typical); PAE: 40 % (typical). Die dimensions: 2.3 × 1.35 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 15000; Maximum: 18000; Value: 15000–18000; Unit: MHz

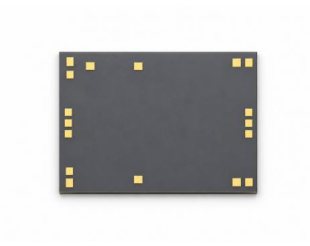
Saturated output power: Symbol: Psat; Typical: 38; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.35; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 19 dBm; τ = 100 µs; D = 10%; pulsed

Product details Product datasheet



LCI-PA-13000-15000-PS42T

13000–15000 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 42 dBm (typical); Power gain: 21 dB (typical); PAE: 35 % (minimum) / 37 % (typical). Die dimensions: 2.8 × 2 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 13000; Maximum: 15000; Value: 13000–15000; Unit: MHz

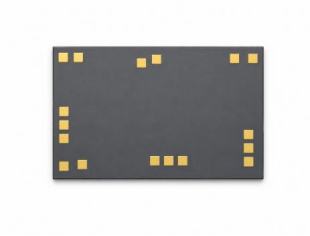
Saturated output power: Symbol: Psat; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.35; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -3.05 V; pulsed

Product details Product datasheet



LCI-TRPA-5000-13000-PS31T

5000–13000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 31 dBm (typical); Power gain: 18 dB (typical); PAE: 30 % (typical). Die dimensions: 2.35 × 1.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 13000; Value: 5000–13000; Unit: MHz

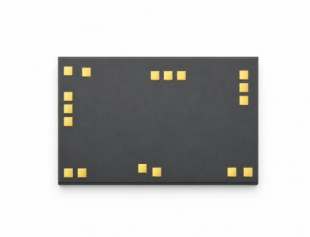
Saturated output power: Symbol: Psat; Typical: 31; Unit: dBm

Power gain: Symbol: Gp; Typical: 18; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +16 V; Vg = -2.8 V

Product details Product datasheet



LCI-TRPA-5000-13000-PS31T-M

5000–13000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 31 dBm (typical); Power gain: 18 dB (typical); PAE: 30 % (typical). Die dimensions: 2.35 × 1.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 13000; Value: 5000–13000; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 31; Unit: dBm

Power gain: Symbol: Gp; Typical: 18; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +16 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-12000-15000-PS47p5T

12000–15000 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 47 dBm (minimum) / 47.5 dBm (typical); Power gain: 22 dB (minimum) / 22.5 dB (typical); PAE: 30 % (minimum) / 34 % (typical). Die dimensions: 4.1 × 5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 12000; Maximum: 15000; Value: 12000–15000; Unit: MHz

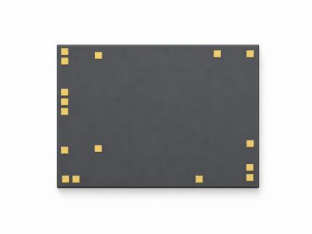
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 22; Typical: 22.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; pulsed

Product details Product datasheet



LCI-TRPA-8000-12000-PS41T

8000–12000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 41 dBm (typical); Power gain: 25 dB (typical); PAE: 38 % (typical). Die dimensions: 3.2 × 2.3 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

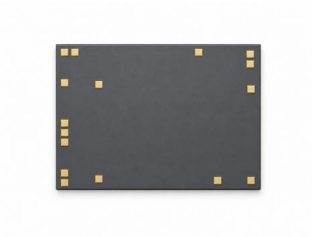
Saturated output power: Symbol: Psat; Typical: 41; Unit: dBm

Power gain: Symbol: Gp; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-TRPA-8000-12000-PS41T-M

8000–12000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 41 dBm (typical); Power gain: 25 dB (typical); PAE: 38 % (typical). Die dimensions: 3.2 × 2.3 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

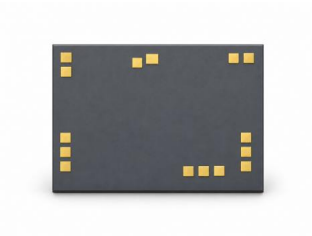
Saturated output power: Symbol: Psat; Typical: 41; Unit: dBm

Power gain: Symbol: Gp; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-TRPA-9000-10000-PS35T

9000–10000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 35 dBm (typical); Power gain: 21 dB (typical); PAE: 35 % (typical). Die dimensions: 2.1 × 1.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 9000; Maximum: 10000; Value: 9000–10000; Unit: MHz

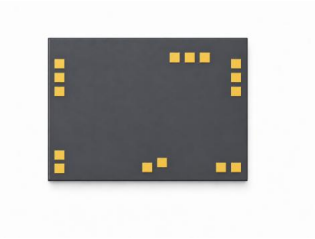
Saturated output power: Symbol: Psat; Typical: 35; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.2; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-TRPA-9000-10000-PS35T-M

9000–10000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 35 dBm (typical); Power gain: 21 dB (typical); PAE: 35 % (typical). Die dimensions: 2.1 × 1.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 9000; Maximum: 10000; Value: 9000–10000; Unit: MHz

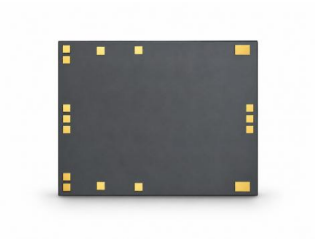
Saturated output power: Symbol: Psat; Typical: 35; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.2; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-15000-17000-PS45T-PG24T

15000–17000 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 45 dBm (typical); Power gain: 24 dB (typical); PAE: 43 % (typical). Die dimensions: 3.1 × 2.45 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 15000; Maximum: 17000; Value: 15000–17000; Unit: MHz

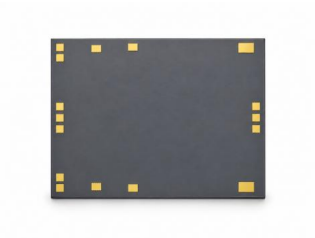
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V; pulsed

Product details Product datasheet



LCI-PA-14000-18000-PS45T

14000–18000 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 45 dBm (typical); Power gain: 24 dB (typical); PAE: 41 % (typical). Die dimensions: 3.1 × 2.45 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V; pulsed

Product details Product datasheet



LCI-PA-15000-18500-PS48T

15000–18500 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 48 dBm (typical); Power gain: 22 dB (typical); PAE: 38 % (typical). Die dimensions: 3.34 × 4.95 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 15000; Maximum: 18500; Value: 15000–18500; Unit: MHz

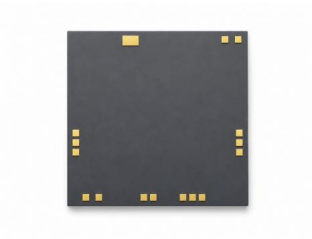
Saturated output power: Symbol: Psat; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V; pulsed

Product details Product datasheet



LCI-TRPA-300-6000-PS39T

300–6000 MHz GaN T/R MMIC Power Amplifier Die

pulsed: PSAT: 38.7 dBm (minimum) / 39 dBm (typical) / 40.5 dBm (maximum); Power gain: 10.7 dB (minimum) / 11 dB (typical) / 12.5 dB (maximum); PAE: 30 % (minimum) / 35 % (typical) / 53 % (maximum). Die dimensions: 3.1 × 3.1 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 300; Maximum: 6000; Value: 300–6000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 38.7; Typical: 39; Maximum: 40.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 10.7; Typical: 11; Maximum: 12.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.9; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; pulsed

Product details Product datasheet



LCI-PA-13750-15350-PS48T

13750–15350 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 47 dBm (minimum) / 48 dBm (typical); Power gain: 19 dB (minimum) / 20 dB (typical); PAE: 35 % (typical). Die dimensions: 3.7 × 5.9 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 13750; Maximum: 15350; Value: 13750–15350; Unit: MHz

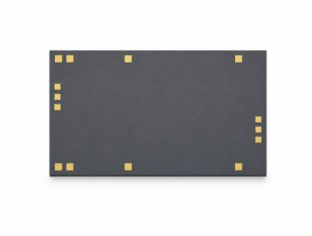
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Id = 0.5 A; pulsed

Product details Product datasheet



LCI-PA-34000-64000-PS30T

34000–64000 MHz GaN MMIC Power Amplifier Die

PSAT: 30 dBm (typical); PAE: 17 % (typical); Power gain: 17 dB (typical). Die dimensions: 3.9 × 2.3 × 0.07 mm.

Operating frequency: Symbol: f; Minimum: 34000; Maximum: 64000; Value: 34000–64000; Unit: MHz

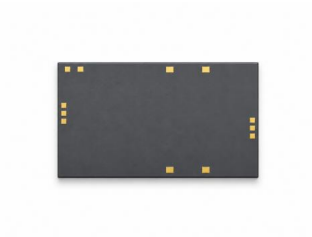
Small-signal gain: Symbol: S21; Typical: 19; Unit: dB

Output power at 1 dB compression: Typical: 27; Unit: dBm

Saturated output power: Symbol: Psat; Typical: 30; Unit: dBm

TA = +25 °C; Vd = +4 V; Id = 0.81 A

Product details Product datasheet



LCI-PA-92000-96000-PS34p5T

92000–96000 MHz MMIC Power Amplifier Die

PSAT: 34.5 dBm (typical); PAE: 14 % (typical); Small-signal gain: 22 dB (typical). Die dimensions: 4.5 × 2.6 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 92000; Maximum: 96000; Value: 92000–96000; Unit: MHz

Small-signal gain: Symbol: S21; Typical: 22; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 34.5; Unit: dBm

TA = +25 °C; Vd = +15 V; Id = 0.28 A

Product details Product datasheet



LCI-LNA-8000-12000-NF0p7T-SG28T

8000–12000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 0.7 dB (typical) / 0.75 dB (maximum); Small-signal gain: 26.5 dB (minimum) / 28 dB (typical); Output 1 dB compression power: 10 dBm (typical). Die dimensions: 1.4 × 0.9 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Output 1 dB compression power: Typical: 10; Unit: dBm

Small-signal gain: Minimum: 26.5; Typical: 28; Unit: dB

Small-signal gain flatness: Typical: ±1.3; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-8000-12000-NF0p7T-SG28T-M

8000–12000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 0.7 dB (typical) / 0.75 dB (maximum); Small-signal gain: 26.5 dB (minimum) / 28 dB (typical); Output 1 dB compression power: 10 dBm (typical). Die dimensions: 1.4 × 0.9 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Output 1 dB compression power: Typical: 10; Unit: dBm

Small-signal gain: Minimum: 26.5; Typical: 28; Unit: dB

Small-signal gain flatness: Typical: ±1.3; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-14000-15000-NF1p1T

14000–15000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 1.1 dB (typical); Small-signal gain: 32 dB (typical); Output 1 dB compression power: 5 dBm (typical). Die dimensions: 1.8 × 1.4 × 0.1 mm.

Operating frequency: Minimum: 14000; Maximum: 15000; Value: 14000–15000; Unit: MHz

Output 1 dB compression power: Typical: 5; Unit: dBm

Small-signal gain: Typical: 32; Unit: dB

Small-signal gain flatness: Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-14000-15000-NF1p1T-M

14000–15000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 1.1 dB (typical); Small-signal gain: 32 dB (typical); Output 1 dB compression power: 5 dBm (typical). Die dimensions: 1.8 × 1.4 × 0.1 mm.

Operating frequency: Minimum: 14000; Maximum: 15000; Value: 14000–15000; Unit: MHz

Output 1 dB compression power: Typical: 5; Unit: dBm

Small-signal gain: Typical: 32; Unit: dB

Small-signal gain flatness: Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-800-4000-NF0p4T

800–4000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 0.4 dB (typical); Small-signal gain: 32 dB (typical) (Vd = +5 V); Output 1 dB compression power: 15 dBm (typical) (Vd = +5 V). Die dimensions: 1.8 × 1.7 × 0.1 mm.

Operating frequency: Minimum: 800; Maximum: 4000; Value: 800–4000; Unit: MHz

Output 1 dB compression power: Typical: 15; Value: Vd = +5 V; Unit: dBm

Small-signal gain: Typical: 32; Value: Vd = +5 V; Unit: dB

Small-signal gain flatness: Typical: ±1.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-800-4000-NF0p4T-M

800–4000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 0.4 dB (typical); Small-signal gain: 32 dB (typical) (Vd = +5 V); Output 1 dB compression power: 15 dBm (typical) (Vd = +5 V). Die dimensions: 1.8 × 1.7 × 0.1 mm.

Operating frequency: Minimum: 800; Maximum: 4000; Value: 800–4000; Unit: MHz

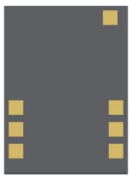
Output 1 dB compression power: Typical: 15; Value: Vd = +5 V; Unit: dBm

Small-signal gain: Typical: 32; Value: Vd = +5 V; Unit: dB

Small-signal gain flatness: Typical: ±1.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-30-600-NF0p6T

30–600 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 0.6 dB (typical); Small-signal gain: 32.3 dB (typical); Input VSWR: 1.2 (typical). Die dimensions: 0.85 × 1.15 × 0.1 mm.

Operating frequency: Minimum: 30; Maximum: 600; Value: 30–600; Unit: MHz

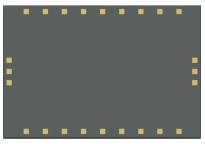
Small-signal gain: Typical: 32.3; Unit: dB

Small-signal gain flatness: Typical: ±0.3; Unit: dB

Input VSWR: Typical: 1.2

TA = +25 °C; Vd = +4 V

Product details Product datasheet



LCI-LNA-75000-110000-NF3p3MAX

75000–110000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 2.8 dB (typical) (f = 90000 MHz); Noise figure: 3.3 dB (maximum); Small-signal gain: 25 dB (typical) (f = 75000–90000 MHz); Small-signal gain: 22 dB (typical) (f = 90000–110000 MHz). Die dimensions: 2 × 3 × 0.1 mm.

Operating frequency: Minimum: 75000; Maximum: 110000; Value: 75000–110000; Unit: MHz

Small-signal gain: Typical: 25; Unit: dB; Notes: f = 75000–90000 MHz

Small-signal gain: Typical: 22; Unit: dB; Notes: f = 90000–110000 MHz

Input return loss: Typical: 6; Unit: dB

TA = +25 °C; VD1–VD4 = +1 V; VG1–VG4 = 0 V; IDtotal = 0.033 A

Product details Product datasheet



LCI-LNA-17000-22000-NF1p3T

17000–22000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 1.3 dB (typical); Small-signal gain: 26 dB (typical); Output 1 dB compression power: 4 dBm (typical). Die dimensions: 1.5 × 0.75 × 0.07 mm.

Operating frequency: Minimum: 17000; Maximum: 22000; Value: 17000–22000; Unit: MHz

Small-signal gain: Typical: 26; Unit: dB

Small-signal gain flatness: Typical: ±0.5; Unit: dB

Noise figure: Typical: 1.3; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LIM-12000-18000-PIP43MAX

12000–18000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.6 dB (typical) / 0.7 dB (maximum); Limiting level: 16.5 dBm (typical) / 17.5 dBm (maximum); Maximum pulsed input power: 43 dBm (maximum) (τ = 1 ms; D = 20%). Die dimensions: 1.4 × 0.8 × 0.1 mm.

Operating frequency: Minimum: 12000; Maximum: 18000; Value: 12000–18000; Unit: MHz

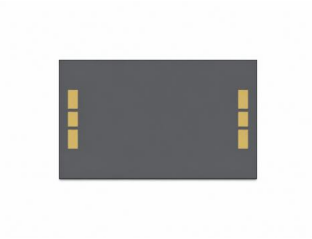
Insertion loss: Typical: 0.6; Maximum: 0.7; Unit: dB

Input VSWR: Typical: 1.4

Output VSWR: Typical: 1.4

TA = +25 °C

Product details Product datasheet



LCI-LIM-5000-6000

5000–6000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.45 dB (typical) / 0.5 dB (maximum); Limiting level: 18.5 dBm (typical) / 19.5 dBm (maximum); Maximum pulsed input power: 49 dBm (maximum) (τ = 2 ms; D = 20%); Maximum pulsed input power: 50 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 2 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

Insertion loss: Typical: 0.45; Maximum: 0.5; Unit: dB

Input VSWR: Typical: 1.2; Maximum: 1.3

Output VSWR: Typical: 1.2; Maximum: 1.3

TA = +25 °C

Product details Product datasheet



LCI-LIM-8000-12000-PIP42MAX

8000–12000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.5 dB (typical); Limiting level: 16 dBm (typical) / 17 dBm (maximum); Maximum pulsed input power: 42 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 2 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

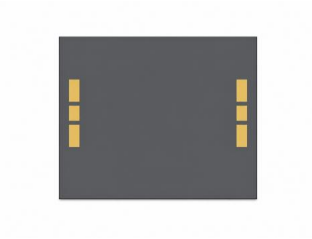
Insertion loss: Typical: 0.5; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCI-LIM-2000-6000-PIP43MAX

2000–6000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.3 dB (typical) / 0.4 dB (maximum); Limiting level: 15 dBm (typical) / 16 dBm (maximum); Maximum pulsed input power: 43 dBm (maximum) (τ = 200 µs; D = 20%). Die dimensions: 1.8 × 1.5 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

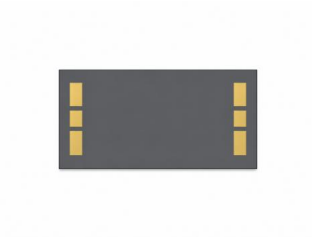
Insertion loss: Typical: 0.3; Maximum: 0.4; Unit: dB

Input VSWR: Typical: 1.4

Output VSWR: Typical: 1.4

TA = +25 °C

Product details Product datasheet



LCI-LIM-6000-18000-PIP42MAX

6000–18000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.8 dB (typical); Limiting level: 16.5 dBm (typical) / 17.5 dBm (maximum); Maximum pulsed input power: 42 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 1.6 × 0.8 × 0.1 mm.

Operating frequency: Minimum: 6000; Maximum: 18000; Value: 6000–18000; Unit: MHz

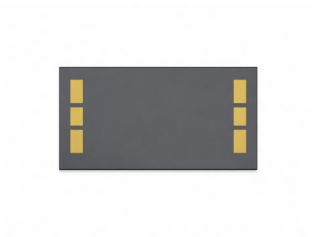
Insertion loss: Typical: 0.8; Unit: dB

Input VSWR: Typical: 1.6

Output VSWR: Typical: 1.6

TA = +25 °C

Product details Product datasheet



LCI-LIM-6000-18000-PIP41MAX

6000–18000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.6 dB (typical); Limiting level: 16 dBm (typical) / 17 dBm (maximum); Maximum pulsed input power: 41 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 1.6 × 0.85 × 0.1 mm.

Operating frequency: Minimum: 6000; Maximum: 18000; Value: 6000–18000; Unit: MHz

Insertion loss: Typical: 0.6; Unit: dB

Input VSWR: Typical: 1.5

Output VSWR: Typical: 1.5

TA = +25 °C

Product details Product datasheet



LCI-LIM-8000-12000-PIP48MAX

8000–12000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.8 dB (typical); Limiting level: 16 dBm (typical) / 17 dBm (maximum); Maximum pulsed input power: 48 dBm (maximum) (τ = 300 µs; D = 30%); Maximum input power: 46 dBm (maximum) (CW). Die dimensions: 1.85 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Insertion loss: Typical: 0.8; Unit: dB

Input VSWR: Typical: 1.5

Output VSWR: Typical: 1.5

TA = +25 °C

Product details Product datasheet



LCI-LIM-DC-14000-PICW37MAX

DC–14000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.4 dB (typical) / 0.5 dB (maximum); Limiting level: 16 dBm (typical) / 17 dBm (maximum); Maximum input power: 37 dBm (maximum) (CW). Die dimensions: 1.25 × 0.65 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 14000; Value: DC–14000; Unit: MHz

Insertion loss: Typical: 0.4; Maximum: 0.5; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCI-LIM-8000-12000-PIP45MAX

8000–12000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.6 dB (typical) / 0.7 dB (maximum); Limiting level: 15 dBm (typical) / 16 dBm (maximum); Maximum pulsed input power: 45 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 2 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Insertion loss: Typical: 0.6; Maximum: 0.7; Unit: dB

Input VSWR: Typical: 1.6

Output VSWR: Typical: 1.6

TA = +25 °C

Product details Product datasheet



LCI-LIM-8000-12000-PIP37MAX

8000–12000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.3 dB (typical); Limiting level: 17 dBm (typical) / 18 dBm (maximum); Maximum pulsed input power: 37 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 1.6 × 0.9 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Insertion loss: Typical: 0.3; Unit: dB

Input VSWR: Typical: 1.2; Maximum: 1.3

Output VSWR: Typical: 1.2; Maximum: 1.3

TA = +25 °C

Product details Product datasheet



LCI-LIM-8000-12000-PIP37MAX-M

8000–12000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.3 dB (typical); Limiting level: 17 dBm (typical) / 18 dBm (maximum); Maximum pulsed input power: 37 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 1.6 × 0.9 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Insertion loss: Typical: 0.3; Unit: dB

Input VSWR: Typical: 1.2; Maximum: 1.3

Output VSWR: Typical: 1.2; Maximum: 1.3

TA = +25 °C

Product details Product datasheet



LCI-LIM-10000-18000-PIP45MAX

10000–18000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.8 dB (typical); Limiting level: 17 dBm (typical) / 18 dBm (maximum); Maximum pulsed input power: 45 dBm (maximum) (τ = 200 µs; D = 30%). Die dimensions: 1.6 × 0.85 × 0.1 mm.

Operating frequency: Minimum: 10000; Maximum: 18000; Value: 10000–18000; Unit: MHz

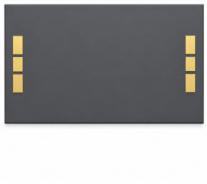
Insertion loss: Typical: 0.8; Unit: dB

Input VSWR: Typical: 1.6; Maximum: 1.8

Output VSWR: Typical: 1.6; Maximum: 1.8

TA = +25 °C

Product details Product datasheet



LCI-LIM-DC-6000-PIP45MAX

DC–6000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.35 dB (typical) / 0.4 dB (maximum); Limiting level: 15 dBm (typical) / 16 dBm (maximum); Maximum pulsed input power: 45 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 2.1 × 1.25 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 6000; Value: DC–6000; Unit: MHz

Insertion loss: Typical: 0.35; Maximum: 0.4; Unit: dB

Input VSWR: Typical: 1.4; Maximum: 1.5

Output VSWR: Typical: 1.4; Maximum: 1.5

TA = +25 °C

Product details Product datasheet



LCI-LIM-2000-4000-PIP51MAX

2000–4000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.4 dB (typical); Limiting level: 16 dBm (typical) / 17 dBm (maximum); Maximum pulsed input power: 51 dBm (maximum) (τ = 100 µs; D = 10%); Maximum input power: 48 dBm (maximum) (CW). Die dimensions: 2.6 × 1.5 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 4000; Value: 2000–4000; Unit: MHz

Insertion loss: Typical: 0.4; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCI-SW-1000-12000-SPDT

1000–12000 MHz GaN SPDT MMIC Switch Die

Insertion loss: 1 dB (typical); Isolation: 34 dB (minimum) / 63 dB (maximum); Input power at 0.2 dB compression: 43 dBm (typical). Die dimensions: 2.45 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 1000; Maximum: 12000; Value: 1000–12000; Unit: MHz

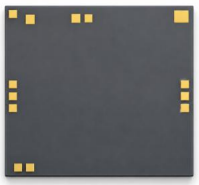
Insertion loss: Typical: 1; Unit: dB

Isolation: Minimum: 34; Maximum: 63; Unit: dB

Input power at 0.2 dB compression: Typical: 43; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-PA-2700-3900-PS31T

2700–3900 MHz GaAs MMIC Power Amplifier Die

pulsed: PSAT: 30.5 dBm (minimum) / 31 dBm (typical); Power gain: 35.5 dB (minimum) / 36 dB (typical); PAE: 45 % (minimum) / 48 % (typical). Plan-view die dimensions: 2.5 × 2.262 mm.

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3900; Value: 2700–3900; Unit: MHz

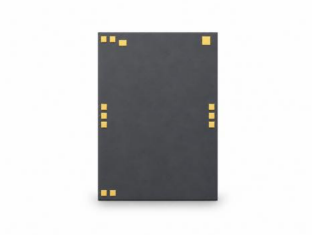
Saturated output power: Symbol: Psat; Minimum: 30.5; Typical: 31; Unit: dBm

Power gain: Symbol: Gp; Minimum: 35.5; Typical: 36; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1.5; Unit: dB

TA = +25 °C; Vd = +8 V; Vg = -0.8 V; Pin = -5 dBm; τ = 100 µs; D = 10%; pulsed

Product details Product datasheet



LCI-PA-2700-3900-PS34p5T

2700–3900 MHz GaAs MMIC Power Amplifier Die

pulsed: PSAT: 34 dBm (minimum) / 34.5 dBm (typical); Power gain: 29 dB (minimum) / 29.5 dB (typical); PAE: 47 % (minimum) / 49 % (typical). Plan-view die dimensions: 2.2 × 3.092 mm.

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3900; Value: 2700–3900; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 34; Typical: 34.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 29; Typical: 29.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +8 V; Vg = -0.7 V; Pin = 5 dBm; τ = 100 µs; D = 10%; pulsed

Product details Product datasheet



LCI-APC-8000-12000-D-G7p5MIN

8000–12000 MHz GaAs MMIC Amplitude and Phase Control RF Front-End Die

Phase step: 5.625 °; Attenuation range: 0–31.5 dB; Output 1 dB compression power: 11 dBm (minimum) / 13 dBm (typical). Die dimensions: 3.8 × 4.7 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Small-signal gain: Minimum: 7.5; Maximum: 10; Value: TX / RX; Unit: dB

Isolation: Minimum: 35; Unit: dB

Attenuation range: Value: 0–31.5; Unit: dB

TA = +25 °C; f(Typ) = 10000 MHz; f(Min/Max) = 8000–12000 MHz

Product details Product datasheet



LCI-BF-14000-18000-4CH

14000–18000 MHz Four-Channel SiGe T/R Beamformer Die

Phase step: 5.625 °; Attenuation range: 0–31.5 dB; Switching time: 100 ns (maximum). Plan-view die dimensions: 5 × 6.2 mm.

Operating frequency: Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

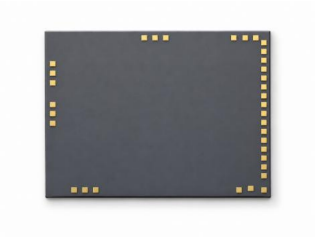
Input/output VSWR: Typical: 1.8

RMS phase error: Maximum: 3; Unit: °

RMS attenuation error: Maximum: 0.3; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-APC-7000-13000

7000–13000 MHz GaAs MMIC Amplitude and Phase Control RF Front-End Die

Phase step: 5.625 ° (typical); Attenuation range: 0.5 dB (minimum) / 31.5 dB (maximum); Small-signal gain: 12 dB (typical) (RX). Die dimensions: 4.55 × 3.54 × 0.1 mm.

Operating frequency: Minimum: 7000; Maximum: 13000; Value: 7000–13000; Unit: MHz

Small-signal gain: Typical: 12; Value: RX; Unit: dB

Output 1 dB compression power: Typical: 11; Value: RX; Unit: dBm

Saturated output power: Typical: 24; Value: TX; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-BF-8000-12000-2CH

8000–12000 MHz Dual-Channel Si T/R Beamformer Die

Phase step: 5.625 ° (typical); Attenuation step: 0.5 dB (typical). Die dimensions: 3.6 × 2.7 × 0.15 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Phase-control resolution: Value: 6; Unit: bit

Attenuation-control resolution: Value: 6; Unit: bit

Phase shift range: Minimum: 0; Maximum: 360; Unit: °

CLK = 50 MHz; RFVDD = AVDD = DVDD = 3.3 V; TA = +27 °C

Product details Product datasheet



LCI-PS-1200-1400-6B-D

1200–1400 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 0.5 ° (minimum) / 0.7 ° (typical) / 1 ° (maximum); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum); Insertion loss: ≈5 dB. Die dimensions: 4 × 1.7 × 0.1 mm.

Operating frequency: Minimum: 1200; Maximum: 1400; Value: 1200–1400; Unit: MHz

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Minimum: 0.5; Typical: 0.7; Maximum: 1; Unit: °

Phase-induced amplitude variation: Typical: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-PS-5000-6000-6B

5000–6000 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1 ° (typical); Insertion loss: 7 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.1 × 1.5 × 0.1 mm.

Operating frequency: Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

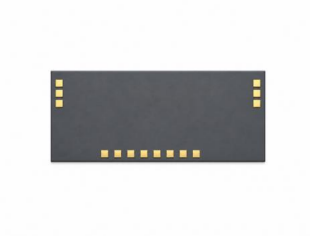
Insertion loss: Typical: 7; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1; Unit: °

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-PS-2700-3500-6B

2700–3500 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1 ° (typical); Insertion loss: 5.5 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.3 × 1.5 × 0.1 mm.

Operating frequency: Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

Insertion loss: Typical: 5.5; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1; Unit: °

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-PS-15000-23000-6B

15000–23000 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1.4 ° (typical); Insertion loss: 9.5 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.1 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 15000; Maximum: 23000; Value: 15000–23000; Unit: MHz

Insertion loss: Typical: 9.5; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1.4; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-25000-33000-6B

25000–33000 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1.6 ° (typical); Insertion loss: 9.5 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.1 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 25000; Maximum: 33000; Value: 25000–33000; Unit: MHz

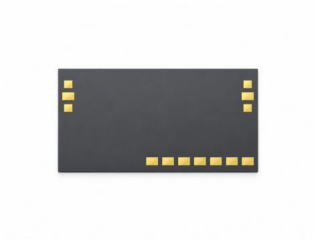
Insertion loss: Typical: 9.5; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1.6; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-14000-18000-6B-D

14000–18000 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1.2 ° (typical); Insertion loss: 7 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 2.5 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

Insertion loss: Typical: 7; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1.2; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-900-1400-6B-D

900–1400 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1.5 ° (typical); Insertion loss: 5 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.6 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 900; Maximum: 1400; Value: 900–1400; Unit: MHz

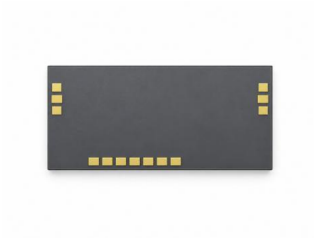
Insertion loss: Typical: 5; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1.5; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-1200-1600-6B-D

1200–1600 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 0.8 ° (typical); Insertion loss: 4.3 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.3 × 1.6 × 0.1 mm.

Operating frequency: Minimum: 1200; Maximum: 1600; Value: 1200–1600; Unit: MHz

Insertion loss: Typical: 4.3; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 0.8; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-2000-8000-6B

2000–8000 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 2.2 ° (typical) / 3 ° (maximum); Insertion loss: 10 dB (typical) / 11.5 dB (maximum); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 5 × 1.75 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 8000; Value: 2000–8000; Unit: MHz

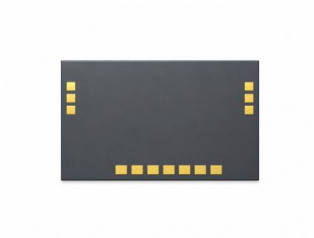
Insertion loss: Typical: 10; Maximum: 11.5; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 2.2; Maximum: 3; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-ATT-14000-18000-6B-D

14000–18000 MHz 6-Bit GaAs MMIC Digital Attenuator Die

RMS attenuation error: 0.3 dB (typical); Insertion loss: 4 dB (maximum); Attenuation range: 0.5 dB (minimum) / 31.5 dB (maximum). Die dimensions: 2.5 × 1.5 × 0.1 mm.

Operating frequency: Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

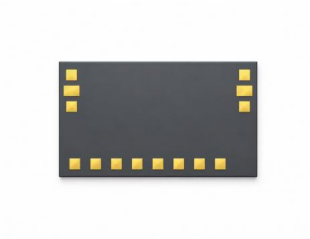
Insertion loss: Maximum: 4; Unit: dB

Attenuation range: Minimum: 0.5; Maximum: 31.5; Unit: dB

RMS attenuation error: Typical: 0.3; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-ATT-DC-8000-6B

DC–8000 MHz 6-Bit GaAs MMIC Digital Attenuator Die

RMS attenuation error: 0.2 dB (typical); Insertion loss: 1.6 dB (typical); Attenuation range: 0.5 dB (minimum) / 31.5 dB (maximum). Die dimensions: 1.9 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 8000; Value: DC–8000; Unit: MHz

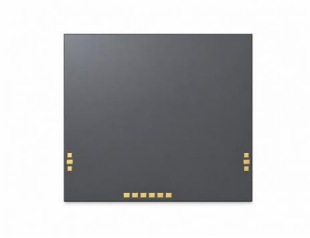
Insertion loss: Typical: 1.6; Unit: dB

Attenuation range: Minimum: 0.5; Maximum: 31.5; Unit: dB

RMS attenuation error: Typical: 0.2; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-TTD-5000-6000-4B

5000–6000 MHz 4-Bit GaAs MMIC Digital Time Delay Die

Time delay: 92.5 ps (typical) (T1; t_nom = 92.59 ps); Time delay: 737 ps (typical) (T4; t_nom = 740.74 ps); Insertion loss: 12 dB (typical) / 13 dB (maximum). Die dimensions: 4.5 × 4 × 0.1 mm.

Operating frequency: Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

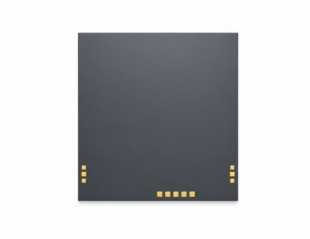
Insertion loss: Typical: 12; Maximum: 13; Unit: dB

Time delay (T1): Typical: 92.5; Value: T1; t_nom = 92.59 ps; Unit: ps

Time delay (T2): Typical: 184; Value: T2; t_nom = 185.185 ps; Unit: ps

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-TTD-8500-10500-4B

8500–10500 MHz 4-Bit GaAs MMIC Digital Time Delay Die

Time delay: 52.7 ps (typical) (T1; t_nom = 52 ps); Time delay: 416 ps (typical) (T4; t_nom = 416 ps); Insertion loss: 12 dB (typical) / 13 dB (maximum). Die dimensions: 4 × 4.2 × 0.1 mm.

Operating frequency: Minimum: 8500; Maximum: 10500; Value: 8500–10500; Unit: MHz

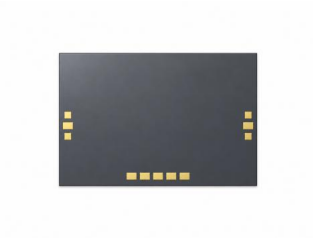
Insertion loss: Typical: 12; Maximum: 13; Unit: dB

Time delay (T1): Typical: 52.7; Value: T1; t_nom = 52 ps; Unit: ps

Time delay (T2): Typical: 102; Value: T2; t_nom = 104 ps; Unit: ps

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-TTD-8000-12000-3B

8000–12000 MHz 3-Bit GaAs MMIC Digital Time Delay Die

Time delay: 25 ps (typical) (T1; t_nom = 25 ps); Time delay: 102 ps (typical) (T3; t_nom = 100 ps); Insertion loss: 6 dB (typical) / 7 dB (maximum). Die dimensions: 3 × 2 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

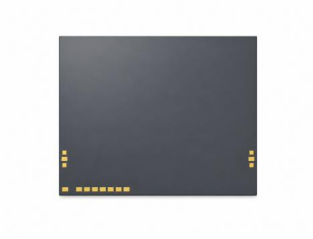
Insertion loss: Typical: 6; Maximum: 7; Unit: dB

Time delay (T1): Typical: 25; Value: T1; t_nom = 25 ps; Unit: ps

Time delay (T2): Typical: 49.5; Value: T2; t_nom = 50 ps; Unit: ps

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-TTD-200-2000-6B

200–2000 MHz 6-Bit GaAs MMIC Digital Time Delay Die

Time delay: 25 ps (typical) (T1; t_nom = 25 ps); Time delay: 800 ps (typical) (T6; t_nom = 800 ps); Insertion loss: 11 dB (maximum). Die dimensions: 5 × 4 × 0.1 mm.

Operating frequency: Minimum: 200; Maximum: 2000; Value: 200–2000; Unit: MHz

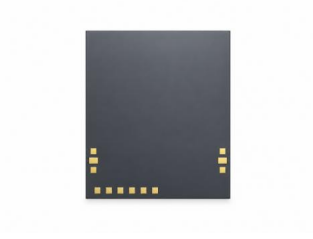
Insertion loss: Maximum: 11; Unit: dB

Time delay (T1): Typical: 25; Unit: ps; Notes: T1; t_nom = 25 ps

Time delay (T2): Typical: 50; Unit: ps; Notes: T2; t_nom = 50 ps

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-TTD-7000-13000-3B

7000–13000 MHz 3-Bit GaAs MMIC Digital Time Delay Die

Time delay: 52 ps (typical) (T1; t_nom = 52 ps); Time delay: 208 ps (typical) (T3; t_nom = 208 ps); Insertion loss: 9 dB (typical). Die dimensions: 2.5 × 2.9 × 0.1 mm.

Operating frequency: Minimum: 7000; Maximum: 13000; Value: 7000–13000; Unit: MHz

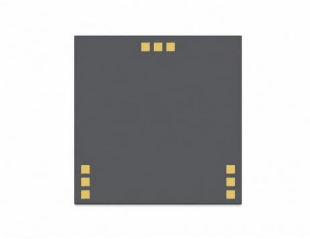
Insertion loss: Typical: 9; Unit: dB

Time delay (T1): Typical: 52; Value: T1; t_nom = 52 ps; Unit: ps

Time delay (T2): Typical: 104; Value: T2; t_nom = 104 ps; Unit: ps

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCDIV-2000-18000-2WAY-D-S2X2

2000–18000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.3 (typical). Die dimensions: 2 × 2 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 18000; Value: 2000–18000; Unit: MHz

Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCDIV-3700-5000-2WAY

3700–5000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.8 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 3700; Maximum: 5000; Value: 3700–5000; Unit: MHz

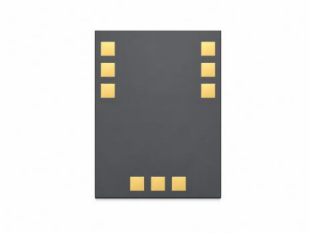
Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-500-2700-2WAY

500–2700 MHz GaAs IPD 2-way 0° power divider die

Isolation: 14 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.3 (typical). Die dimensions: 0.9 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 500; Maximum: 2700; Value: 500–2700; Unit: MHz

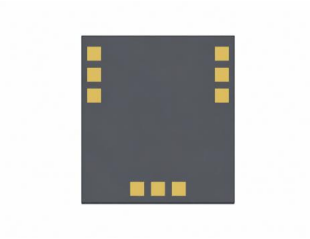
Isolation: Typical: 14; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCDIV-800-2000-2WAY

800–2000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 18 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.3 (typical). Die dimensions: 1.1 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 800; Maximum: 2000; Value: 800–2000; Unit: MHz

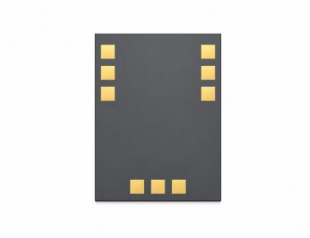
Isolation: Typical: 18; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCDIV-1000-4000-2WAY

1000–4000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 18 dB (typical); Input VSWR: 1.4 (typical); Output VSWR: 1.4 (typical). Die dimensions: 0.9 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 1000; Maximum: 4000; Value: 1000–4000; Unit: MHz

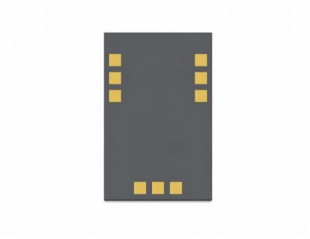
Isolation: Typical: 18; Unit: dB

Input VSWR: Typical: 1.4

Output VSWR: Typical: 1.4

TA = +25 °C

Product details Product datasheet



LCDIV-2000-6000-2WAY

2000–6000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.9 × 1.4 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

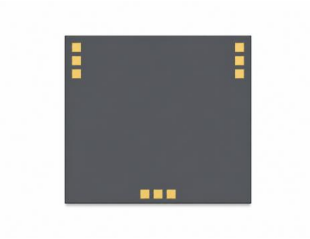
Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-2000-18000-2WAY-D-S2p12X1p9

2000–18000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.3 (typical). Die dimensions: 2.12 × 1.9 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 18000; Value: 2000–18000; Unit: MHz

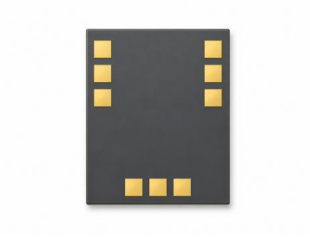
Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCDIV-2700-3500-2WAY

2700–3500 MHz GaAs IPD 2-way 0° power divider die

Isolation: 30 dB (typical); Input VSWR: 1.1 (typical); Output VSWR: 1.1 (typical). Die dimensions: 0.9 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

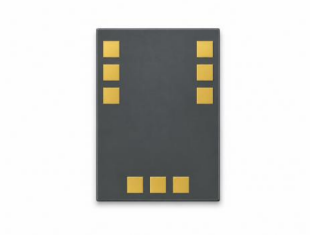
Isolation: Typical: 30; Unit: dB

Input VSWR: Typical: 1.1

Output VSWR: Typical: 1.1

TA = +25 °C

Product details Product datasheet



LCDIV-5000-7000-2WAY

5000–7000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 25 dB (typical); Input VSWR: 1.1 (typical); Output VSWR: 1.1 (typical). Die dimensions: 0.8 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 5000; Maximum: 7000; Value: 5000–7000; Unit: MHz

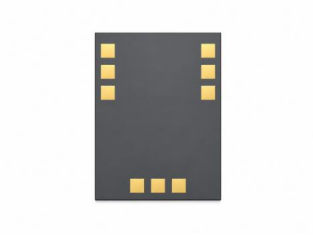
Isolation: Typical: 25; Unit: dB

Input VSWR: Typical: 1.1

Output VSWR: Typical: 1.1

TA = +25 °C

Product details Product datasheet



LCDIV-5000-13000-2WAY

5000–13000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 25 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.9 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 5000; Maximum: 13000; Value: 5000–13000; Unit: MHz

Isolation: Typical: 25; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-6000-18000-2WAY

6000–18000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.8 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 6000; Maximum: 18000; Value: 6000–18000; Unit: MHz

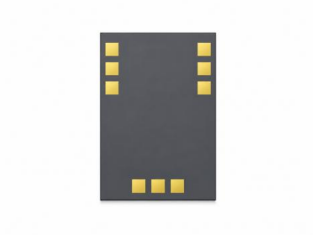
Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-7000-13000-2WAY

7000–13000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 25 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.9 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 7000; Maximum: 13000; Value: 7000–13000; Unit: MHz

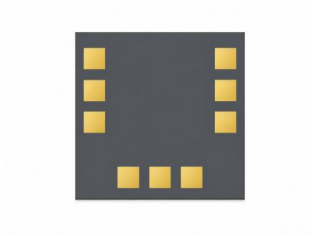
Isolation: Typical: 25; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-8000-12000-2WAY

8000–12000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.1 (typical). Die dimensions: 0.8 × 0.8 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

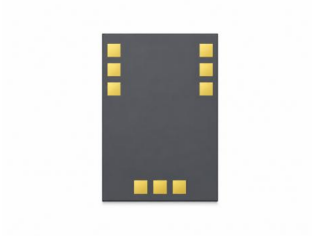
Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.1

TA = +25 °C

Product details Product datasheet



LCDIV-10000-20000-2WAY

10000–20000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 30 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.9 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 10000; Maximum: 20000; Value: 10000–20000; Unit: MHz

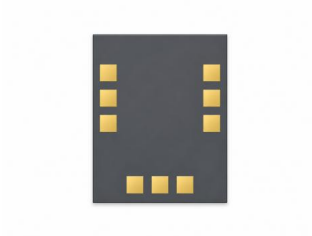
Isolation: Typical: 30; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-12000-18000-2WAY

12000–18000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 25 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.1 (typical). Die dimensions: 0.8 × 1 × 0.1 mm.

Operating frequency: Minimum: 12000; Maximum: 18000; Value: 12000–18000; Unit: MHz

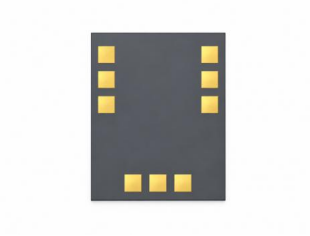
Isolation: Typical: 25; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.1

TA = +25 °C

Product details Product datasheet



LCDIV-30000-40000-2WAY

30000–40000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.3 (typical). Die dimensions: 0.8 × 1 × 0.1 mm.

Operating frequency: Minimum: 30000; Maximum: 40000; Value: 30000–40000; Unit: MHz

Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCRES-R15OHM

15 Ω GaAs thin-film resistor die

Resistance: 15 Ω (typical); Linear operating current: 0.35 A (typical); Maximum allowable current: 0.8 A (maximum). Plan-view die dimensions: 0.5 × 0.5 mm.

Resistor count: Value: 1

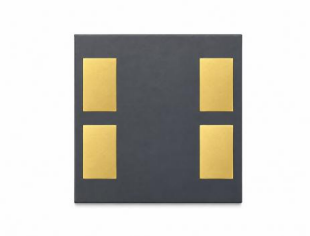
Terminal count: Value: 2

Resistance: Typical: 15; Unit: Ω

Resistance tolerance: Typical: ±5; Unit: %

TA = +25 °C

Product details Product datasheet



LCRES-N2-R20OHM

2 × 20 Ω GaAs thin-film resistor die

Resistance: 20 / 20 Ω (typical); Linear operating current: 0.165 / 0.165 A (typical); Maximum allowable current: 0.33 A (maximum). Plan-view die dimensions: 0.5 × 0.5 mm.

Resistor count: Value: 2

Terminal count: Value: 4

Resistance: Typical: 20 / 20; Unit: Ω

Resistance tolerance: Typical: ±5; Unit: %

TA = +25 °C

Product details Product datasheet



LCRES-R50OHM

50 Ω GaAs thin-film resistor die

Resistance: 50 Ω (typical); Linear operating current: 0.2 A (typical); Maximum allowable current: 0.6 A (maximum). Plan-view die dimensions: 0.5 × 0.5 mm.

Resistor count: Value: 1

Terminal count: Value: 2

Resistance: Typical: 50; Unit: Ω

Resistance tolerance: Typical: ±5; Unit: %

TA = +25 °C

Product details Product datasheet



LCRES-R1000OHM

1000 Ω GaAs thin-film resistor die

Resistance: 1000 Ω (typical); Linear operating current: 0.04 A (typical); Maximum allowable current: 0.08 A (maximum). Plan-view die dimensions: 0.5 × 0.5 mm.

Resistor count: Value: 1

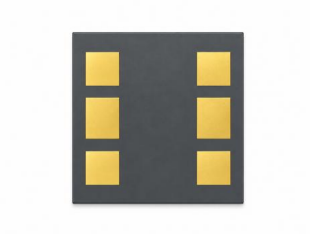
Terminal count: Value: 2

Resistance: Typical: 1000; Unit: Ω

Resistance tolerance: Typical: ±5; Unit: %

TA = +25 °C

Product details Product datasheet



LCCAP-C10PF

10 pF GaAs capacitor die

Capacitance: 10 pF (typical); Withstand voltage: 50 V (typical). Die dimensions: 0.5 × 0.5 × 0.1 mm.

Capacitance: Typical: 10; Unit: pF; TA = +25 °C

Withstand voltage: Typical: 50; Unit: V; TA = +25 °C

Breakdown voltage: Value: 80 (Vb); Unit: V

Storage temperature: Minimum: -65; Maximum: 150; Unit: °C

Product details Product datasheet



LCEQ-8000-12000-D

8000–12000 MHz GaAs slope equalizer die

Equalization amount: 2 dB; Insertion loss @ 8000 MHz: 2.6 dB; Insertion loss @ 12000 MHz: 0.7 dB. Die dimensions: 0.8 × 0.8 × 0.1 mm.

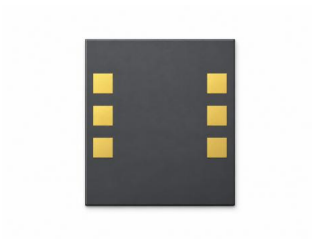
Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Equalization amount: Value: 2; Unit: dB

Insertion loss @ 8000 MHz: Value: 2.6; Unit: dB

Insertion loss @ 12000 MHz: Value: 0.7; Unit: dB

Product details Product datasheet



LCEQ-2000-6000-D

2000–6000 MHz GaAs slope equalizer die

Equalization amount: 5.5 dB; Insertion loss @ 2000 MHz: 0.6 dB; Insertion loss @ 6000 MHz: 6.1 dB. Die dimensions: 0.8 × 0.9 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

Equalization amount: Value: 5.5; Unit: dB

Insertion loss @ 2000 MHz: Value: 0.6; Unit: dB

Insertion loss @ 6000 MHz: Value: 6.1; Unit: dB

Product details Product datasheet



LCATT-DC-30000-A0-S0p35X0p35

DC–30000 MHz 0 dB GaAs IPD fixed attenuator die

Attenuation: 0 dB; Input/output VSWR: 1.2 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 0; Unit: dB

Input/output VSWR: Value: 1.2

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A1-S0p35X0p35

DC–30000 MHz 1 dB GaAs IPD fixed attenuator die

Attenuation: 1 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 1; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A2-S0p35X0p35

DC–30000 MHz 2 dB GaAs IPD fixed attenuator die

Attenuation: 2 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.4 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 2; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.4; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A3-S0p35X0p35

DC–30000 MHz 3 dB GaAs IPD fixed attenuator die

Attenuation: 3 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.4 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 3; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.4; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A4

DC–30000 MHz 4 dB GaAs IPD fixed attenuator die

Attenuation: 4 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.4 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 4; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.4; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A8-S0p35X0p35

DC–30000 MHz 8 dB GaAs IPD fixed attenuator die

Attenuation: 8 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.3 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 8; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.3; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A16

DC–30000 MHz 16 dB GaAs IPD fixed attenuator die

Attenuation: 16 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.3 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 16; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.3; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A0-S0p5X0p35

DC–30000 MHz 0 dB GaAs IPD fixed attenuator die

Attenuation: 0 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.6 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 0; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.6; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A1-S0p5X0p35

DC–30000 MHz 1 dB GaAs IPD fixed attenuator die

Attenuation: 1 dB; Input/output VSWR: 1.4 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 1; Unit: dB

Input/output VSWR: Value: 1.4

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A2-S0p5X0p35

DC–30000 MHz 2 dB GaAs IPD fixed attenuator die

Attenuation: 2 dB; Input/output VSWR: 1.35 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 2; Unit: dB

Input/output VSWR: Value: 1.35

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A3-S0p5X0p35

DC–30000 MHz 3 dB GaAs IPD fixed attenuator die

Attenuation: 3 dB; Input/output VSWR: 1.35 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 3; Unit: dB

Input/output VSWR: Value: 1.35

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A5

DC–30000 MHz 5 dB GaAs IPD fixed attenuator die

Attenuation: 5 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 5; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A6

DC–30000 MHz 6 dB GaAs IPD fixed attenuator die

Attenuation: 6 dB; Input/output VSWR: 1.35 ; Attenuation flatness: ±0.4 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 6; Unit: dB

Input/output VSWR: Value: 1.35

Attenuation flatness: Value: ±0.4; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A8-S0p5X0p35

DC–30000 MHz 8 dB GaAs IPD fixed attenuator die

Attenuation: 8 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.3 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 8; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.3; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A10

DC–30000 MHz 10 dB GaAs IPD fixed attenuator die

Attenuation: 10 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 10; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCXOV-DC-40000-D

DC–40000 MHz GaAs RF crossover die

Insertion loss: 0.4 dB (typical); Isolation: 30 dB (typical); Return loss: 20 dB (typical). Die dimensions: 0.6 × 0.6 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 40000; Value: DC–40000; Unit: MHz

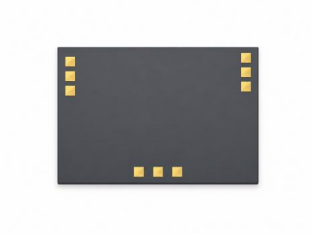
Insertion loss: Typical: 0.4; Unit: dB

Isolation: Typical: 30; Unit: dB

Return loss: Typical: 20; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-MIX-500-2000-D

500–2000 MHz GaAs MMIC Passive Double-Balanced Mixer Die

Conversion loss: 9 dB (typical); LO power: 15 dBm; Operating frequency (IF): 0 MHz (minimum) / 900 MHz (maximum) / DC–900 MHz. Die dimensions: 2.1 × 1.45 × 0.1 mm.

Operating frequency: Minimum: 500; Maximum: 2000; Value: 500–2000 (RF / LO); Unit: MHz

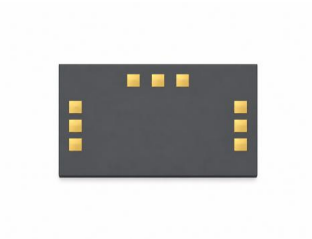
Operating frequency (IF): Minimum: 0; Maximum: 900; Value: DC–900; Unit: MHz

Conversion loss: Typical: 9; Unit: dB

Isolation (LO / RF): Typical: 45; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-MIX-7000-10000-D

7000–10000 MHz GaAs MMIC Passive Double-Balanced Mixer Die

Conversion loss: 8.5 dB (typical); LO power: 14 dBm; Operating frequency (IF): 1400 MHz (minimum) / 3000 MHz (maximum) / 1400–3000 MHz. Die dimensions: 1.6 × 0.9 × 0.1 mm.

Operating frequency: Minimum: 7000; Maximum: 10000; Value: 7000–10000 (RF); Unit: MHz

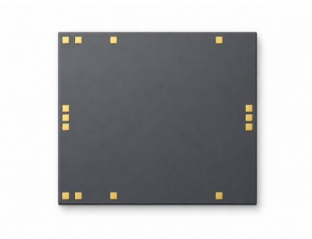
Operating frequency (LO): Minimum: 5000; Maximum: 9000; Value: 5000–9000; Unit: MHz

Operating frequency (IF): Minimum: 1400; Maximum: 3000; Value: 1400–3000; Unit: MHz

Conversion loss: Typical: 8.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-PA-6000-18000-PS42T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 42 dBm (typical); Power gain: 17 dB (typical); Power-added efficiency: 20 % (typical); Die dimensions: 3.9 × 3.4 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 41.2; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Minimum: 16.2; Typical: 17; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-8000-12000-PS29T

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 29 dBm (typical); Power gain: 14 dB (typical); Power-added efficiency: 15 % (typical); Die dimensions: 1.95 × 1.35 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

Power gain: Symbol: Gp; Minimum: 13; Typical: 14; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.5; Unit: dB

Saturated output power: Symbol: Psat; Typical: 29; Unit: dBm

TA = +25 °C; Vd = +28 V

Product details Product datasheet



LCI-PA-4000-8000-PS43p5T

4000–8000 MHz GaN MMIC Power Amplifier Die

4000–8000 MHz; PSAT 43.5 dBm (typical); Power gain 20.5 dB (typical); PAE 40% (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 8000; Unit: MHz

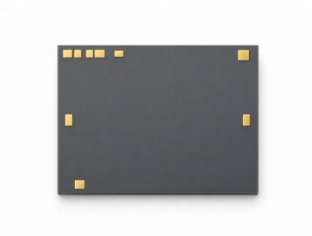
Saturated output power: Symbol: Psat; Minimum: 43; Typical: 43.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 20; Typical: 20.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-2000-6000-PS40p5T

2000–6000 MHz GaN MMIC Power Amplifier Die

2000–6000 MHz; Saturated output power: 40.5 dBm (typical); Power gain: 22.5 dB (typical); Power-added efficiency: 38 % (typical); Die dimensions: 2.8 × 2.1 mm.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Unit: MHz

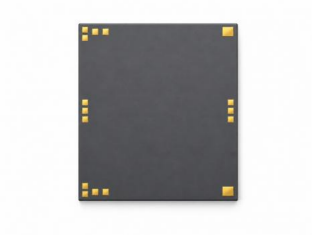
Saturated output power: Symbol: Psat; Minimum: 39.5; Typical: 40.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21.5; Typical: 22.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V; Pin = 18 dBm; CW

Product details Product datasheet



LCI-PA-2000-6000-PS45p8T

2000–6000 MHz GaN MMIC Power Amplifier Die

2000–6000 MHz; Saturated output power: 45.8 dBm (typical); Power gain: 18.8 dB (typical); Power-added efficiency: 42 % (typical); Die dimensions: 3.17 × 3.58 mm.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Unit: MHz

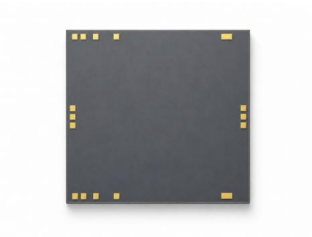
Saturated output power: Symbol: Psat; Minimum: 44.8; Typical: 45.8; Unit: dBm

Power gain: Symbol: Gp; Minimum: 17.8; Typical: 18.8; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 27 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-4000-10000-PS45T

4000–10000 MHz GaN MMIC Power Amplifier Die

4000–10000 MHz; Saturated output power: 45 dBm (typical); Power gain: 17 dB (typical); Power-added efficiency: 30 % (typical); Die dimensions: 4.1 × 3.9 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 10000; Unit: MHz

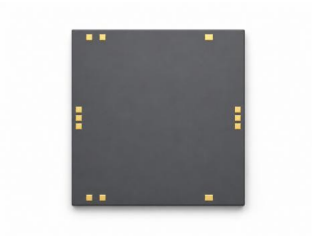
Saturated output power: Symbol: Psat; Minimum: 43.8; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Minimum: 15.8; Typical: 17; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-2500-6200-PS45p5T

2500–6200 MHz GaN MMIC Power Amplifier Die

2500–6200 MHz; PSAT 45.5 dBm (typical); Power gain 17.5 dB (typical); PAE 40% (typical).

Operating frequency: Symbol: f; Minimum: 2500; Maximum: 6200; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 45; Typical: 45.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 17; Typical: 17.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-8500-10500-PS47p8T

8500–10500 MHz GaN MMIC Power Amplifier Die

8500–10500 MHz; Saturated output power: 47.8 dBm (typical); Power gain: 21.8 dB (typical); Power-added efficiency: 47 % (typical); Die dimensions: 4 × 5.1 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 8500; Maximum: 10500; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.8; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21; Typical: 21.8; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-8000-12000-PS42T-D

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 42 dBm (typical); Power gain: 22 dB (typical); Power-added efficiency: 43 % (typical); Die dimensions: 3.04 × 1.91 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 41.2; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21.2; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-2000-18000-PS40T

2000–18000 MHz GaN MMIC Power Amplifier Die

2000–18000 MHz; PSAT 40 dBm (typical); Power gain 12 dB (typical); PAE 20% (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 18000; Unit: MHz

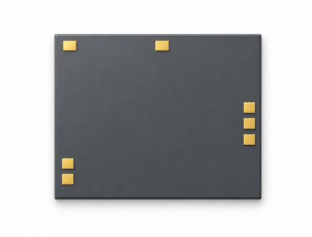
Saturated output power: Symbol: Psat; Typical: 40; Unit: dBm

Power gain: Symbol: Gp; Typical: 12; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -1.8 V

Product details Product datasheet



LCI-PA-6000-18000-PS33p5T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 33.5 dBm (typical); Power gain: 12 dB (typical); Power-added efficiency: 20 % (typical); Die dimensions: 2.1 × 1.7 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

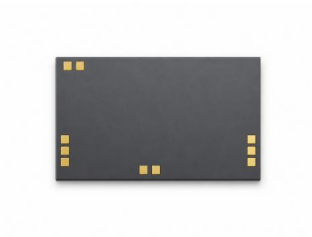
Saturated output power: Symbol: Psat; Minimum: 33; Typical: 33.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 11; Typical: 12; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2 V

Product details Product datasheet



LCI-PA-2000-18000-PS35T

2000–18000 MHz GaN MMIC Power Amplifier Die

2000–18000 MHz; PSAT 35 dBm (typical); Power gain 7 dB (typical); PAE 20% (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 18000; Unit: MHz

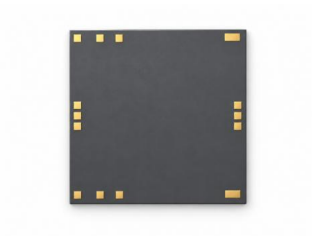
Saturated output power: Symbol: Psat; Typical: 35; Unit: dBm

Power gain: Symbol: Gp; Typical: 7; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.5 V

Product details Product datasheet



LCI-PA-9200-10400-PS46p2T

9200–10400 MHz GaN MMIC Power Amplifier Die

9200–10400 MHz; Saturated output power: 46.2 dBm (typical); Power gain: 24.2 dB (typical); Power-added efficiency: 50 % (typical); Die dimensions: 3 × 3.03 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 9200; Maximum: 10400; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 46; Typical: 46.2; Maximum: 46.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24; Typical: 24.2; Maximum: 24.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-7500-10500-PS49T

7500–10500 MHz GaN MMIC Power Amplifier Die

7500–10500 MHz; Saturated output power: 49 dBm (typical); Power gain: 25 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 3.7 × 6 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 7500; Maximum: 10500; Unit: MHz

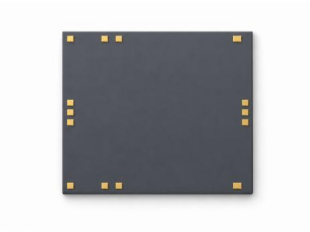
Saturated output power: Symbol: Psat; Minimum: 48.6; Typical: 49; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24.6; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-7000-13000-PS45T

7000–13000 MHz GaN MMIC Power Amplifier Die

7000–13000 MHz; Saturated output power: 45 dBm (typical); Power gain: 22 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 3.5 × 3.2 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 7000; Maximum: 13000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 44; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-6000-18000-PS45T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 45 dBm (typical); Power gain: 20 dB (typical); Power-added efficiency: 23 % (typical); Die dimensions: 4.52 × 5.82 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 44.5; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19.5; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-5000-6000-PS49p5T

5000–6000 MHz GaN MMIC Power Amplifier Die

5000–6000 MHz; Saturated output power: 49.5 dBm (typical); Power gain: 26.5 dB (typical); Power-added efficiency: 50 % (typical); Die dimensions: 3.5 × 5.8 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 6000; Unit: MHz

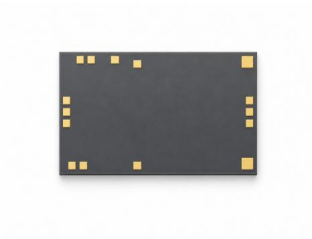
Saturated output power: Symbol: Psat; Minimum: 49; Typical: 49.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 26; Typical: 26.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.2; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-6000-18000-PS40T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 40 dBm (typical); Power gain: 19 dB (typical); Power-added efficiency: 23 % (typical); Die dimensions: 3 × 1.8 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

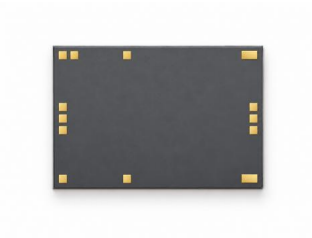
Saturated output power: Symbol: Psat; Minimum: 39; Typical: 40; Unit: dBm

Power gain: Symbol: Gp; Minimum: 18; Typical: 19; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V; Pin = 21 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-10000-18000-PS41T

10000–18000 MHz GaN MMIC Power Amplifier Die

10000–18000 MHz; Saturated output power: 41 dBm (typical); Power gain: 19 dB (typical); Power-added efficiency: 30 % (typical); Die dimensions: 3.2 × 2.25 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 10000; Maximum: 18000; Unit: MHz

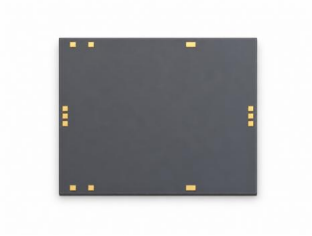
Saturated output power: Symbol: Psat; Minimum: 40.9; Typical: 41; Unit: dBm

Power gain: Symbol: Gp; Minimum: 18.9; Typical: 19; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-950-1250-PS47p5T

950–1250 MHz GaN MMIC Power Amplifier Die

950–1250 MHz; Saturated output power: 47.5 dBm (typical); Power gain: 22.5 dB (typical); Power-added efficiency: 60 % (typical); Die dimensions: 4.35 × 3.43 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 950; Maximum: 1250; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 22; Typical: 22.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-5000-6000-PS47p5T

5000–6000 MHz GaN MMIC Power Amplifier Die

5000–6000 MHz; Saturated output power: 47.5 dBm (typical); Power gain: 24.5 dB (typical); Power-added efficiency: 53 % (typical); Die dimensions: 3.1 × 3.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 6000; Unit: MHz

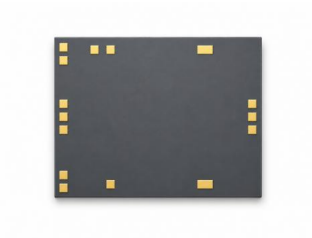
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24; Typical: 24.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.4; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-8000-12000-PS43p5T

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 43.5 dBm (typical); Power gain: 22.5 dB (typical); Power-added efficiency: 45 % (typical); Die dimensions: 2.7 × 2.08 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 43; Typical: 43.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 22; Typical: 22.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-8000-12000-PS39T-D

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 39 dBm (typical); Power gain: 18 dB (typical); Power-added efficiency: 43 % (typical); Die dimensions: 2.3 × 1.15 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 38; Typical: 39; Unit: dBm

Power gain: Symbol: Gp; Minimum: 17; Typical: 18; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.7; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-8500-10500-PS52T

8500–10500 MHz GaN MMIC Power Amplifier Die

8500–10500 MHz; Saturated output power: 52 dBm (typical); Power gain: 24 dB (typical); Power-added efficiency: 45 % (typical); Die dimensions: 3.9 × 6.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8500; Maximum: 10500; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 52; Unit: dBm

Power gain: Symbol: Gp; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +48 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-4000-8000-PS47p5T

4000–8000 MHz GaN MMIC Power Amplifier Die

4000–8000 MHz; PSAT 47.5 dBm (typical); Power gain 17.5 dB (typical); PAE 40% (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 8000; Unit: MHz

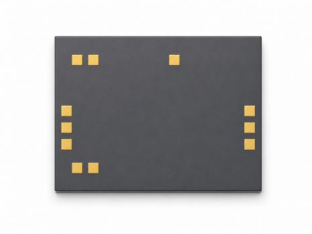
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 17; Typical: 17.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-4000-8000-PS37T

4000–8000 MHz GaN MMIC Power Amplifier Die

4000–8000 MHz; PSAT 37 dBm (typical); Power gain 20 dB (typical); PAE 35% (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 8000; Unit: MHz

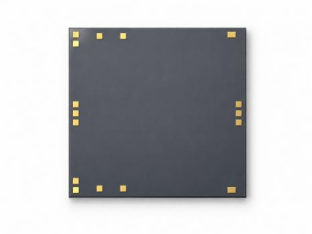
Saturated output power: Symbol: Psat; Minimum: 36.5; Typical: 37; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19.5; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V

Product details Product datasheet



LCI-PA-8000-12000-PS47T

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 47 dBm (typical); Power gain: 25 dB (typical); Power-added efficiency: 45 % (typical); Die dimensions: 3.5 × 3.6 × 0.1 mm. RF test conditions: Vd = +28 V; Vg = -2.6 V.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

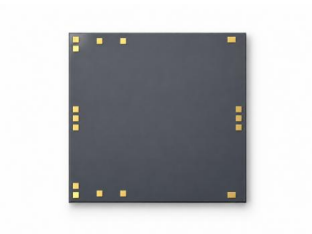
Saturated output power: Symbol: Psat; Minimum: 46.5; Typical: 47; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24.5; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-8000-12000-PS47T-B

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 47 dBm (typical); Power gain: 25 dB (typical); Power-added efficiency: 45 % (typical); Die dimensions: 3.5 × 3.6 × 0.1 mm. RF test conditions: Vd = +28 V; Vg = -1.8 V.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

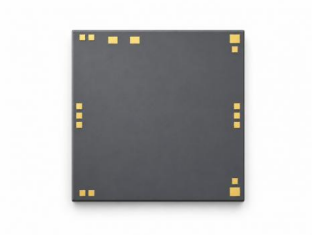
Saturated output power: Symbol: Psat; Minimum: 46.5; Typical: 47; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24.5; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -1.8 V

Product details Product datasheet



LCI-PA-3600-5000-PS44p5T

3600–5000 MHz GaN MMIC Power Amplifier Die

3600–5000 MHz; PSAT 44.5 dBm (typical); Power gain 23.5 dB (typical); PAE 43% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 3600; Maximum: 5000; Unit: MHz

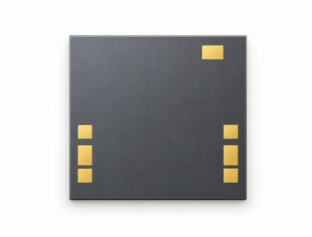
Saturated output power: Symbol: Psat; Minimum: 44; Typical: 44.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 23; Typical: 23.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 21 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-5000-13000-PS25T

5000–13000 MHz GaN MMIC Power Amplifier Die

5000–13000 MHz; Saturated output power: 25 dBm (typical); Power gain: 10 dB (typical); Die dimensions: 1.3 × 1.25 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 13000; Unit: MHz

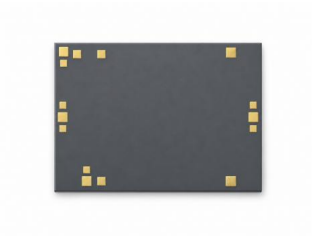
Saturated output power: Symbol: Psat; Typical: 25; Unit: dBm

Power gain: Symbol: Gp; Typical: 10; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Pin = 15 dBm; °CW

Product details Product datasheet



LCI-PA-5000-13000-PS42T

5000–13000 MHz GaN MMIC Power Amplifier Die

5000–13000 MHz; Saturated output power: 42 dBm (typical); Power gain: 20 dB (typical); Power-added efficiency: 35 % (typical); Die dimensions: 3.1 × 2.26 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 13000; Unit: MHz

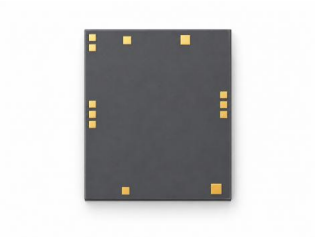
Saturated output power: Symbol: Psat; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-4200-7000-PS42T

4200–7000 MHz GaN MMIC Power Amplifier Die

4200–7000 MHz; PSAT 42 dBm (typical); Power gain 22 dB (typical); PAE 45% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 4200; Maximum: 7000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 41.8; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21.8; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 20 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2000-6000-PS45p5T

2000–6000 MHz GaN MMIC Power Amplifier Die

2000–6000 MHz; PSAT 45.5 dBm (typical); Power gain 20.5 dB (typical); PAE 35% (typical); CW; Vd = +24 V.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Unit: MHz

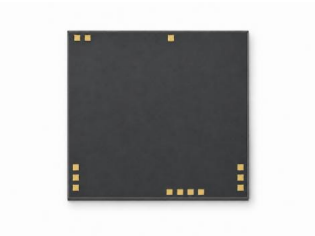
Saturated output power: Symbol: Psat; Minimum: 45; Typical: 45.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 20; Typical: 20.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1.5; Unit: dB

TA = +25 °C; Vd = +24 V; Vg = -2.4 V; Pin = 25 dBm; CW

Product details Product datasheet



LCI-PA-200-2200-PS41p5T

200–2200 MHz GaN MMIC Power Amplifier Die

GaN-on-SiC power amplifier die for 200–2200 MHz, with 41.5 dBm typical saturated output, 25.5 dB typical power gain and a 3.00 × 3.00 × 0.10 mm outline.

Operating frequency: Symbol: f; Minimum: 200; Maximum: 2200; Unit: MHz

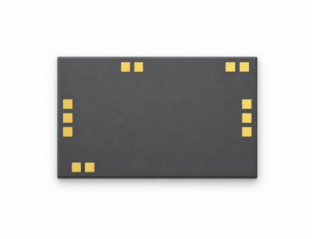
Saturated output power: Symbol: Psat; Minimum: 41.0; Typical: 41.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 25.0; Typical: 25.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.0; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = −2.6 V

Product details Product datasheet



LCI-PA-3400-5600-PS40T

3400–5600 MHz GaN MMIC Power Amplifier Die

3400–5600 MHz; PSAT 40 dBm (typical); Power gain 17 dB (typical); PAE 46% (typical); CW.

Operating frequency: Symbol: f; Minimum: 3400; Maximum: 5600; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 39; Typical: 40; Unit: dBm

Power gain: Symbol: Gp; Minimum: 16; Typical: 17; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 23 dBm; CW

Product details Product datasheet



LCI-PA-5800-6800-PS47T

5800–6800 MHz GaN MMIC Power Amplifier Die

5800–6800 MHz; Saturated output power: 47 dBm (typical); Power gain: 21 dB (typical); Power-added efficiency: 46 % (typical); Die dimensions: 3.5 × 5.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5800; Maximum: 6800; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 47; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-2700-3500-PS45p5T-D

2700–3500 MHz GaN MMIC Power Amplifier Die

2700–3500 MHz; PSAT 45.5 dBm (typical); Power gain 25.5 dB (typical); PAE 58% (typical); CW.

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 45; Typical: 45.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 25; Typical: 25.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 20 dBm; CW

Product details Product datasheet



LCI-PA-6700-7400-PS41T

6700–7400 MHz GaN MMIC Power Amplifier Die

6700–7400 MHz; Saturated output power: 41 dBm (typical); Power gain: 22 dB (typical); Power-added efficiency: 55 % (typical); Die dimensions: 3.2 × 2 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6700; Maximum: 7400; Unit: MHz

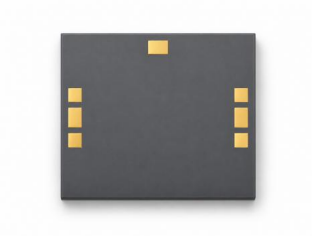
Saturated output power: Symbol: Psat; Typical: 41; Unit: dBm

Power gain: Symbol: Gp; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-6000-18000-PS27T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 27 dBm (typical); Power gain: 9 dB (typical); Die dimensions: 1.5 × 1.3 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

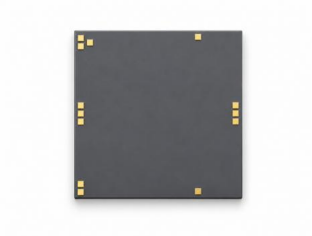
Saturated output power: Symbol: Psat; Minimum: 26; Typical: 27; Maximum: 29; Unit: dBm

Power gain: Symbol: Gp; Minimum: 8; Typical: 9; Maximum: 11; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +28 V; Pin = 18 dBm; °CW

Product details Product datasheet



LCI-PA-2000-8000-PS42T

2000–8000 MHz GaN MMIC Power Amplifier Die

2000–8000 MHz; PSAT 42 dBm (typical); Power gain 15 dB (typical); PAE 30% (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 8000; Unit: MHz

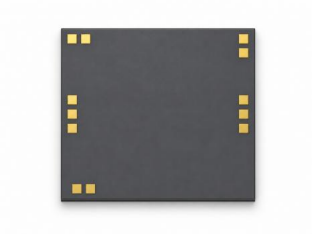
Saturated output power: Symbol: Psat; Minimum: 41; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Minimum: 14; Typical: 15; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-2500-3700-PS41p5T

2500–3700 MHz GaN MMIC Power Amplifier Die

2500–3700 MHz; PSAT 41.5 dBm (typical); Power gain 22.5 dB (typical); PAE 50% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2500; Maximum: 3700; Unit: MHz

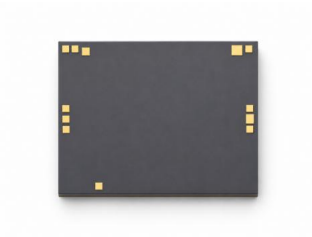
Saturated output power: Symbol: Psat; Minimum: 41; Typical: 41.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 22; Typical: 22.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 19 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2600-3300-PS45p5T

2600–3300 MHz GaN MMIC Power Amplifier Die

2600–3300 MHz; PSAT 45.5 dBm (typical); Power gain 25.5 dB (typical); PAE 60% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2600; Maximum: 3300; Unit: MHz

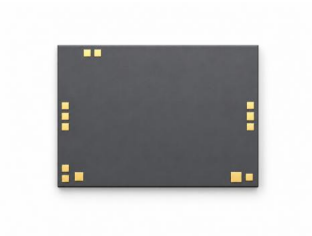
Saturated output power: Symbol: Psat; Minimum: 45; Typical: 45.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 25; Typical: 25.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 20 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2400-3800-PS46p5T

2400–3800 MHz GaN MMIC Power Amplifier Die

2400–3800 MHz; PSAT 46.5 dBm (typical); Power gain 27.5 dB (typical); PAE 56% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2400; Maximum: 3800; Unit: MHz

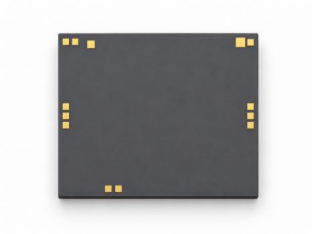
Saturated output power: Symbol: Psat; Minimum: 46; Typical: 46.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 27; Typical: 27.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 19 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2500-4000-PS47T

2500–4000 MHz GaN MMIC Power Amplifier Die

2500–4000 MHz; PSAT 47 dBm (typical); Power gain 26 dB (typical); PAE 52% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2500; Maximum: 4000; Unit: MHz

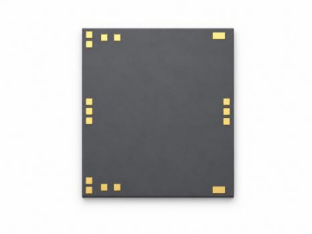
Saturated output power: Symbol: Psat; Minimum: 46.2; Typical: 47; Unit: dBm

Power gain: Symbol: Gp; Minimum: 25.2; Typical: 26; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.3 V; Pin = 21 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-8000-9400-PS45T

8000–9400 MHz GaN MMIC Power Amplifier Die

8000–9400 MHz; Saturated output power: 45 dBm (typical); Power gain: 31 dB (typical); Power-added efficiency: 52 % (typical); Die dimensions: 3 × 3.2 × 0.1 mm. RF test conditions: Vd = +28 V; Vg = -2.8 V.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 9400; Unit: MHz

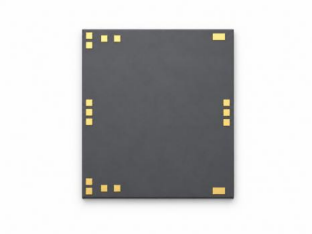
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 31; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-8000-9400-PS45T-A

8000–9400 MHz GaN MMIC Power Amplifier Die

8000–9400 MHz; Saturated output power: 45 dBm (typical); Power gain: 31 dB (typical); Power-added efficiency: 52 % (typical); Die dimensions: 3 × 3.2 × 0.1 mm. RF test conditions: Vd = +28 V; Vg = -1.8 V.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 9400; Unit: MHz

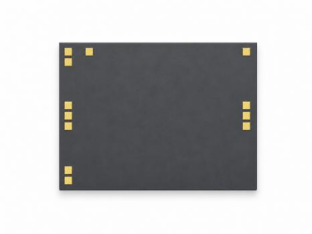
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 31; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -1.8 V

Product details Product datasheet



LCI-PA-1200-1600-PS43p5T

1200–1600 MHz GaN MMIC Power Amplifier Die

1200–1600 MHz; Saturated output power: 43.5 dBm (typical); Power gain: 17 dB (typical); Power-added efficiency: 60 % (typical); Die dimensions: 2.7 × 2 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 1200; Maximum: 1600; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 43.5; Unit: dBm

Power gain: Symbol: Gp; Typical: 17; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-8000-18000-PS46p5T

8000–18000 MHz GaN MMIC Power Amplifier Die

8000–18000 MHz; Saturated output power: 46.5 dBm (typical); Power gain: 18 dB (typical); Power-added efficiency: 28 % (typical); Die dimensions: 4 × 5.6 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 18000; Unit: MHz

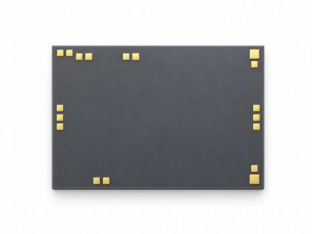
Saturated output power: Symbol: Psat; Minimum: 46; Typical: 46.5; Maximum: 47.5; Unit: dBm

Power gain: Symbol: Gp; Typical: 18; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-4400-6500-PS44T

4400–6500 MHz GaN MMIC Power Amplifier Die

4400–6500 MHz; Saturated output power: 44 dBm (typical); Power gain: 27 dB (typical); Power-added efficiency: 47 % (typical); Die dimensions: 3.51 × 2.44 mm.

Operating frequency: Symbol: f; Minimum: 4400; Maximum: 6500; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 43.5; Typical: 44; Unit: dBm

Power gain: Symbol: Gp; Minimum: 26.5; Typical: 27; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 17 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2700-3500-PS43p5T

2700–3500 MHz GaN MMIC Power Amplifier Die

2700–3500 MHz; PSAT 43.5 dBm (typical); Power gain 26.5 dB (typical); PAE 61% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Unit: MHz

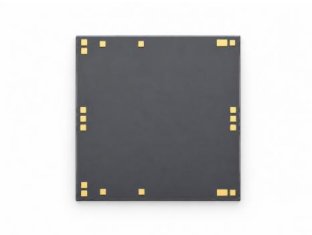
Saturated output power: Symbol: Psat; Minimum: 43; Typical: 43.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 26; Typical: 26.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 0.6; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 17 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-10800-13000-PS45T

10800–13000 MHz GaN MMIC Power Amplifier Die

10800–13000 MHz; Saturated output power: 45 dBm (typical); Power gain: 21 dB (typical); Power-added efficiency: 38 % (typical); Die dimensions: 3.4 × 3.52 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 10800; Maximum: 13000; Unit: MHz

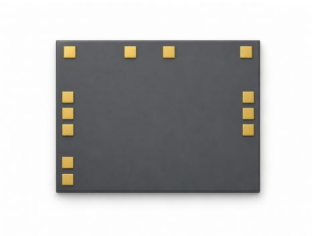
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-9000-11000-PS37T

9000–11000 MHz GaN MMIC Power Amplifier Die

9000–11000 MHz; Saturated output power: 37 dBm (typical); Power gain: 22 dB (typical); Power-added efficiency: 38 % (typical); Die dimensions: 2.04 × 1.54 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 9000; Maximum: 11000; Unit: MHz

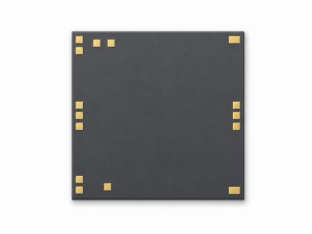
Saturated output power: Symbol: Psat; Typical: 37; Unit: dBm

Power gain: Symbol: Gp; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.2; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-8000-8400-PS45T

8000–8400 MHz GaN MMIC Power Amplifier Die

8000–8400 MHz; Saturated output power: 45 dBm (typical); Power gain: 23 dB (typical); Power-added efficiency: 55 % (typical); Die dimensions: 2.9 × 2.8 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 8400; Unit: MHz

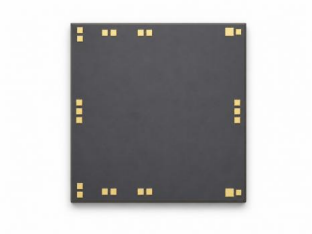
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 23; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -3 V

Product details Product datasheet



LCI-PA-3700-5000-PS45p2T

3700–5000 MHz GaN MMIC Power Amplifier Die

3700–5000 MHz; PSAT 45.2 dBm (typical); Power gain 27 dB (typical); PAE 48% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 3700; Maximum: 5000; Unit: MHz

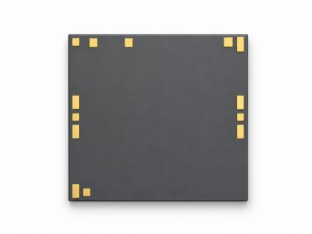
Saturated output power: Symbol: Psat; Minimum: 45; Typical: 45.2; Unit: dBm

Power gain: Symbol: Gp; Minimum: 26.8; Typical: 27; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 18 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2000-6000-PS43T-D

2000–6000 MHz GaN MMIC Power Amplifier Die

2000–6000 MHz; Saturated output power: 43 dBm (typical); Power gain: 26.5 dB (typical); Power-added efficiency: 50 % (typical); Die dimensions: 3.1 × 2.9 mm.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Unit: MHz

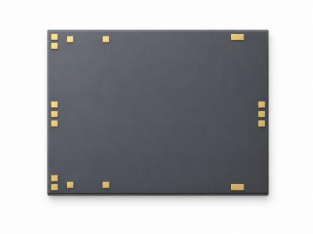
Saturated output power: Symbol: Psat; Minimum: 42.5; Typical: 43; Unit: dBm

Power gain: Symbol: Gp; Minimum: 25.5; Typical: 26.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 0.6; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V; Pin = 17 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-6000-18000-PS44T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 44 dBm (typical); Power gain: 20 dB (typical); Power-added efficiency: 30 % (typical); Die dimensions: 4 × 3.3 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 44; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-8000-18000-PS44T

8000–18000 MHz GaN MMIC Power Amplifier Die

8000–18000 MHz; Saturated output power: 44 dBm (typical); Power gain: 19 dB (typical); Power-added efficiency: 30 % (typical); Die dimensions: 3.5 × 4 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 18000; Unit: MHz

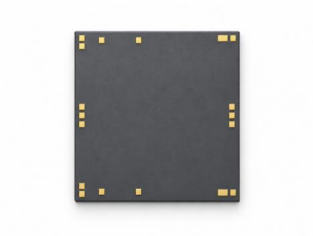
Saturated output power: Symbol: Psat; Typical: 44; Unit: dBm

Power gain: Symbol: Gp; Typical: 19; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-10000-13000-PS45T

10000–13000 MHz GaN MMIC Power Amplifier Die

10000–13000 MHz; Saturated output power: 45 dBm (typical); Power gain: 20 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 3.3 × 3.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 10000; Maximum: 13000; Unit: MHz

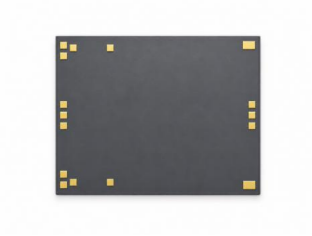
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-8000-18000-PS43p5T

8000–18000 MHz GaN MMIC Power Amplifier Die

8000–18000 MHz; Saturated output power: 43.5 dBm (typical); Power gain: 19.5 dB (typical); Power-added efficiency: 30 % (typical); Die dimensions: 3.2 × 2.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 18000; Unit: MHz

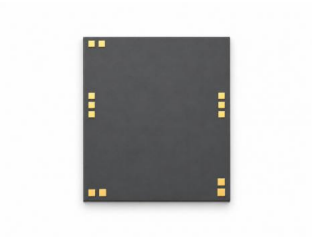
Saturated output power: Symbol: Psat; Typical: 43.5; Unit: dBm

Power gain: Symbol: Gp; Typical: 19.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V

Product details Product datasheet



LCI-PA-2000-2800-PS41T

2000–2800 MHz GaN MMIC Power Amplifier Die

2000–2800 MHz; Saturated output power: 41 dBm (typical); Power gain: 24 dB (typical); Power-added efficiency: 56 % (typical); Die dimensions: 2.4 × 2.7 mm.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 2800; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 40.7; Typical: 41; Unit: dBm

Power gain: Symbol: Gp; Minimum: 23.7; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; Pin = 17 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-300-6000-PS40p8T

300–6000 MHz GaN MMIC Power Amplifier Die

300–6000 MHz; Saturated output power: 40.8 dBm (typical); Power gain: 12.8 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 2.95 × 2.4 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 300; Maximum: 6000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 40; Typical: 40.8; Maximum: 41.6; Unit: dBm

Power gain: Symbol: Gp; Minimum: 12; Typical: 12.8; Maximum: 13.6; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V

Product details Product datasheet



LCI-PA-2000-18500-PS43T

2000–18500 MHz GaN MMIC Power Amplifier Die

2000–18500 MHz; PSAT 43 dBm (typical); Power gain 13 dB (typical); PAE 20% (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 18500; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 43; Unit: dBm

Power gain: Symbol: Gp; Typical: 13; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2 V

Product details Product datasheet



LCI-PA-1950-4050-PS46p5T

1950–4050 MHz GaN MMIC Power Amplifier Die

1950–4050 MHz; Saturated output power: 46.5 dBm (typical); Power gain: 24.5 dB (typical); Power-added efficiency: 52 % (typical); Die dimensions: 3.56 × 3.78 mm.

Operating frequency: Symbol: f; Minimum: 1950; Maximum: 4050; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 46; Typical: 46.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24; Typical: 24.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; Pin = 22 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-300-6000-PS30T

300–6000 MHz GaN MMIC Power Amplifier Die

300–6000 MHz; Saturated output power: 30 dBm (typical); Power gain: 15 dB (typical); Power-added efficiency: 15 % (typical); Die dimensions: 2.15 × 2.46 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 300; Maximum: 6000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 28; Typical: 30; Maximum: 32.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 13; Typical: 15; Maximum: 17.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±2.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-2700-3900-PS48T

2700–3900 MHz GaN MMIC Power Amplifier Die

2700–3900 MHz; PSAT 48 dBm (typical); Power gain 24 dB (typical); PAE 56% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3900; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 47.6; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Minimum: 23.6; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.6; Unit: dB

Vd = +28 V; Vg = -2.7 V; Pin = 24 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-10000-13000-PS30p5T

10000–13000 MHz GaN MMIC Power Amplifier Die

10000–13000 MHz; Saturated output power: 30.5 dBm (typical); Power gain: 30 dB (typical); Power-added efficiency: 22 % (typical); Die dimensions: 2.22 × 1.16 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 10000; Maximum: 13000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 30; Typical: 30.5; Unit: dBm

Power gain: Symbol: Gp; Typical: 30; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V

Product details Product datasheet



LCI-PA-10000-13000-PS48T

10000–13000 MHz GaN MMIC Power Amplifier Die

10000–13000 MHz; Saturated output power: 48 dBm (typical); Power gain: 20 dB (typical); Power-added efficiency: 37 % (typical); Die dimensions: 3.4 × 5.74 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 10000; Maximum: 13000; Unit: MHz

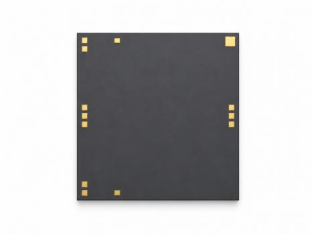
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Id = 2.2 A

Product details Product datasheet



LCI-PA-1200-2400-PS45T

1200–2400 MHz GaN MMIC Power Amplifier Die

1200–2400 MHz; Saturated output power: 45 dBm (typical); Power gain: 25 dB (typical); Power-added efficiency: 53 % (typical); Die dimensions: 3.1 × 3.2 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 1200; Maximum: 2400; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 44.5; Typical: 45; Maximum: 45.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24.5; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-6000-12000-PS48T

6000–12000 MHz GaN MMIC Power Amplifier Die

6000–12000 MHz; Saturated output power: 48 dBm (typical); Power gain: 24 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 3.85 × 5.82 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 12000; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-7000-13000-PS48T

7000–13000 MHz GaN MMIC Power Amplifier Die

7000–13000 MHz; Saturated output power: 48 dBm (typical); Power gain: 24 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 3.83 × 5.82 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 7000; Maximum: 13000; Unit: MHz

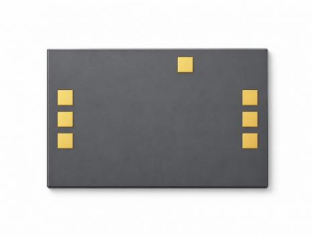
Saturated output power: Symbol: Psat; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-LNA-5000-6000-NF0p6T

5000–6000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.6 dB (typical)

5000–6000 MHz; NF 0.6 dB (typical); Small-signal gain 28 dB (typical); P1dB 6 dBm (typical).

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

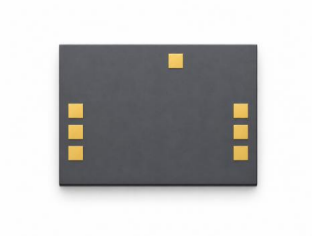
Output 1 dB compression power: Symbol: P1dB; Typical: 6; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 28; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-7000-13000-NF0p9T

7000–13000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.9 dB (typical)

7000–13000 MHz; NF 0.9 dB (typical); Small-signal gain 22 dB (typical); P1dB 14 dBm (typical).

Operating frequency: Symbol: f; Minimum: 7000; Maximum: 13000; Value: 7000–13000; Unit: MHz

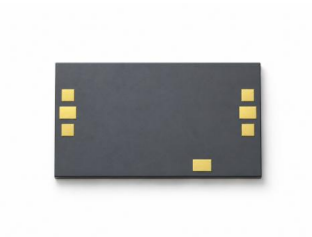
Output 1 dB compression power: Symbol: P1dB; Typical: 14; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 22; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Maximum: ±0.4; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-7000-13000-NF1T

7000–13000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 1 dB (typical)

7000–13000 MHz; NF 1 dB (typical); Small-signal gain ≥ 28 dB; P1dB 6 dBm (typical).

Operating frequency: Symbol: f; Minimum: 7000; Maximum: 13000; Value: 7000–13000; Unit: MHz

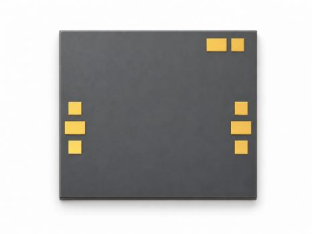
Output 1 dB compression power: Symbol: P1dB; Typical: 6; Unit: dBm

Small-signal gain: Symbol: Gain; Minimum: 28; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±2; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-2000-6000-NF0p8T

2000–6000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.8 dB (typical)

2000–6000 MHz; NF 0.8 dB (typical); Small-signal gain ≥ 29 dB; P1dB 10 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

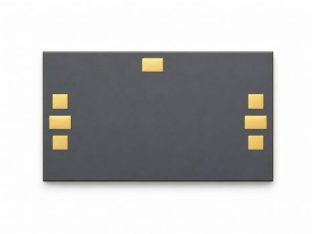
Output 1 dB compression power: Symbol: P1dB; Typical: 10; Unit: dBm

Small-signal gain: Symbol: Gain; Minimum: 29; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.2; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-6000-18000-NF1p2T

6000–18000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 1.2 dB (typical)

6000–18000 MHz; NF 1.2 dB (typical); Small-signal gain 22 dB (typical); P1dB 8 dBm (typical).

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Value: 6000–18000; Unit: MHz

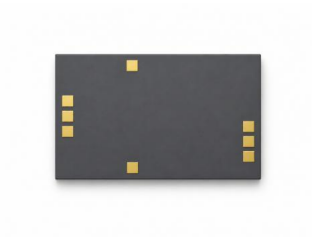
Output 1 dB compression power: Symbol: P1dB; Typical: 8; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 22; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±2; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-24000-40000-NF2p5T

24000–40000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 2.5 dB (typical)

24000–40000 MHz; NF 2.5 dB (typical); Small-signal gain 23 dB (typical); P1dB ≥ 11 dBm.

Operating frequency: Symbol: f; Minimum: 24000; Maximum: 40000; Value: 24000–40000; Unit: MHz

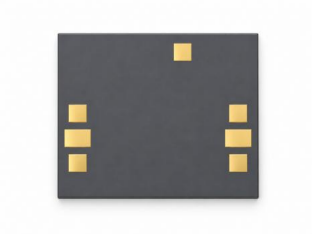
Output 1 dB compression power: Symbol: P1dB; Minimum: 11; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 23; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V; Vg = 0 V

Product details Product datasheet



LCI-LNA-8000-12000-NF0p7T-SG26T

8000–12000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.7 dB (typical)

8000–12000 MHz; NF 0.7 dB (typical); Small-signal gain 26 dB (typical); P1dB 8 dBm (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

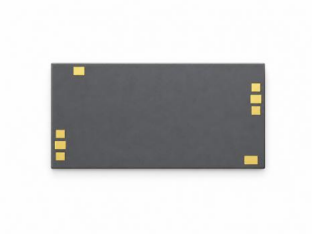
Output 1 dB compression power: Symbol: P1dB; Minimum: 7; Typical: 8; Unit: dBm

Small-signal gain: Symbol: Gain; Minimum: 25; Typical: 26; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-2000-20000-NF2T

2000–20000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 2 dB (typical)

2000–20000 MHz; NF 2 dB (typical); Small-signal gain 17 dB (typical); P1dB 14 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 20000; Value: 2000–20000; Unit: MHz

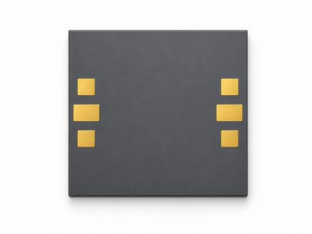
Output 1 dB compression power: Symbol: P1dB; Typical: 14; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 17; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V; Vg = 0 V

Product details Product datasheet



LCI-LNA-100-2000-NF1p1T

100–2000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 1.1 dB (typical)

100–2000 MHz; NF 1.1 dB (typical); Small-signal gain 17.5 dB (typical); P1dB 19.5 dBm (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 2000; Value: 100–2000; Unit: MHz

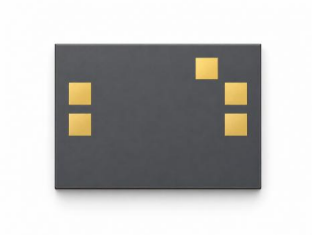
Output 1 dB compression power: Symbol: P1dB; Typical: 19.5; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 17.5; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-800-2000-NF0p45T

800–2000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.45 dB (typical)

800–2000 MHz; NF 0.45 dB (typical); Small-signal gain 23 dB (typical); P1dB 20.5 dBm (typical).

Operating frequency: Symbol: f; Minimum: 800; Maximum: 2000; Value: 800–2000; Unit: MHz

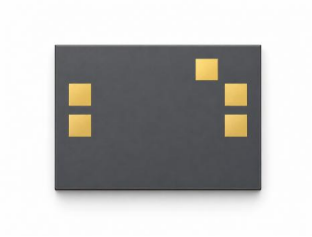
Output 1 dB compression power: Symbol: P1dB; Typical: 20.5; Unit: dBm

Saturated output power: Symbol: Psat; Value: 22; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 23; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-200-600-NF0p4T

200–600 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.4 dB (typical)

200–600 MHz; NF 0.4 dB (typical); Small-signal gain 28 dB (typical); P1dB 21 dBm (typical).

Operating frequency: Symbol: f; Minimum: 200; Maximum: 600; Value: 200–600; Unit: MHz

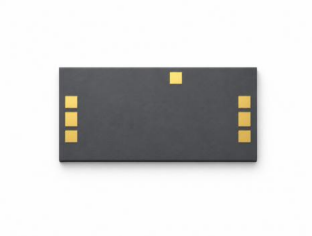
Output 1 dB compression power: Symbol: P1dB; Typical: 21; Unit: dBm

Saturated output power: Symbol: Psat; Value: 22.5; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 28; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-2000-5000-NF0p45T-P1DB14T

2000–5000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.45 dB (typical); P1dB 14 dBm (typical)

2000–5000 MHz; NF 0.45 dB (typical); Small-signal gain 30 dB (typical); P1dB 14 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 5000; Value: 2000–5000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 14; Unit: dBm

Saturated output power: Symbol: Psat; Value: 15; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 30; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-7000-9000-NF0p6U

7000–9000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.6 dB

7000–9000 MHz; NF 0.6 dB; Small-signal gain 31 dB (typical); P1dB 15 dBm (typical).

Operating frequency: Symbol: f; Minimum: 7000; Maximum: 9000; Value: 7000–9000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 15; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 31; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-6000-20000-NF1p2T

6000–20000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 1.2 dB (typical)

6000–20000 MHz; NF 1.2 dB (typical); Small-signal gain 26 dB (typical); P1dB -2 dBm (typical).

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 20000; Value: 6000–20000; Unit: MHz

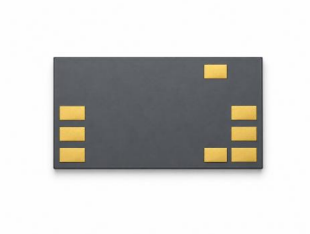
Output 1 dB compression power: Symbol: P1dB; Minimum: -4; Typical: -2; Maximum: 0; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 26; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-4000-12000-NF0p6T

4000–12000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.6 dB (typical)

4000–12000 MHz; NF 0.6 dB (typical); Small-signal gain 34.5 dB (typical); P1dB 7 dBm (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 12000; Value: 4000–12000; Unit: MHz

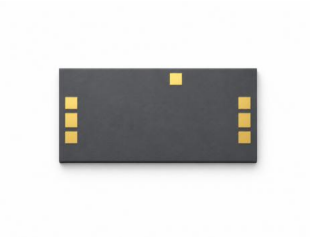
Output 1 dB compression power: Symbol: P1dB; Minimum: 6.5; Typical: 7; Maximum: 8.5; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 34.5; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.2; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-2000-5000-NF0p45T-P1DB11T

2000–5000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.45 dB (typical); P1dB 11 dBm (typical)

2000–5000 MHz; NF 0.45 dB (typical); Small-signal gain 30 dB (typical); P1dB 11 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 5000; Value: 2000–5000; Unit: MHz

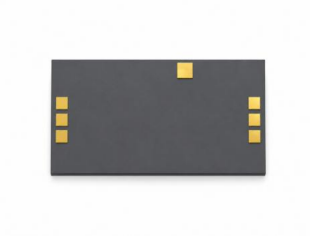
Output 1 dB compression power: Symbol: P1dB; Typical: 11; Unit: dBm

Saturated output power: Symbol: Psat; Value: 12; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 30; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-32000-52000-NF1p8T

32000–52000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 1.8 dB (typical)

32000–52000 MHz; NF 1.8 dB (typical); Small-signal gain 26 dB (typical); P1dB 5 dBm (typical).

Operating frequency: Symbol: f; Minimum: 32000; Maximum: 52000; Value: 32000–52000; Unit: MHz

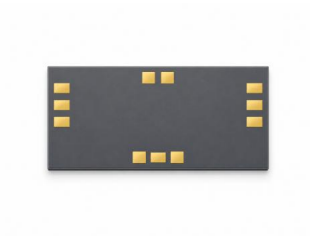
Output 1 dB compression power: Symbol: P1dB; Typical: 5; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 26; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-SW-12000-18000-SPDT

12000–18000 MHz GaN SPDT MMIC Switch Die — IL 1 dB (typical)

12000–18000 MHz; Insertion loss 1 dB (typical); Isolation 38 dB (typical); P0.2dB 44 dBm (typical).

Operating frequency: Symbol: f; Minimum: 12000; Maximum: 18000; Value: 12000–18000; Unit: MHz

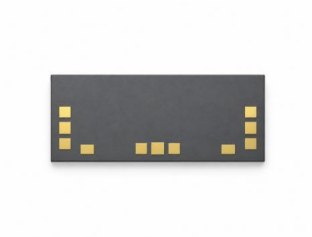
Insertion loss: Typical: 1; Maximum: 1.2; Unit: dB

Isolation: Minimum: 36; Typical: 38; Unit: dB

Input power at 0.2 dB compression: Typical: 44; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-SW-32000-38000-SPDT

32000–38000 MHz SPDT MMIC Switch Die — IL 1 dB (typical)

32000–38000 MHz; Insertion loss 1 dB (typical); Isolation 20 dB (typical); P0.2dB 42 dBm (typical).

Operating frequency: Symbol: f; Minimum: 32000; Maximum: 38000; Value: 32000–38000; Unit: MHz

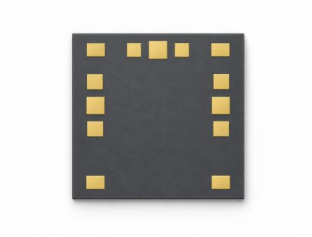
Insertion loss: Typical: 1; Unit: dB

Isolation: Typical: 20; Unit: dB

Input power at 0.2 dB compression: Typical: 42; Unit: dBm

Von = -28 V; Voff = 0 V; TA = +25 °C

Product details Product datasheet



LCI-SW-2000-18000-SPDT

2000–18000 MHz SPDT MMIC Switch Die — IL 0.9 dB (typical)

2000–18000 MHz; Insertion loss 0.9 dB (typical); Isolation 23 dB (typical); P0.2dB 37 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 18000; Value: 2000–18000; Unit: MHz

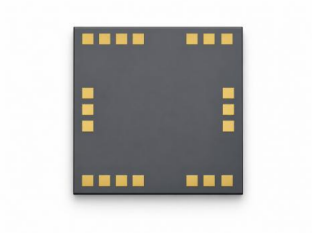
Insertion loss: Typical: 0.9; Unit: dB

Isolation: Typical: 23; Unit: dB

Input power at 0.2 dB compression: Typical: 37; Unit: dBm

Von = +28 V; Voff = 0 V; TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SP3T-D

100–20000 MHz GaAs SP3T MMIC Switch Die — IL ≤ 2.8 dB (2000–20000 MHz)

100–20000 MHz; Insertion loss (100–2000 MHz) ≤ 1.4 dB; Isolation (100–2000 MHz) ≤ 65 dB.

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz

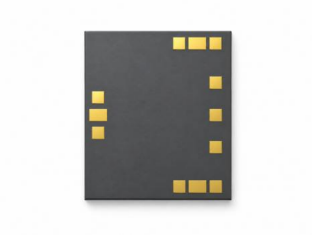
Insertion loss (100–2000 MHz): Maximum: 1.4; Value: f = 100–2000 MHz; Unit: dB

Insertion loss (2000–20000 MHz): Maximum: 2.8; Value: f = 2000–20000 MHz; Unit: dB

Isolation (100–2000 MHz): Maximum: 65; Value: f = 100–2000 MHz; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SPDT-D-IL1p6T

100–20000 MHz GaAs SPDT MMIC Switch Die — IL 1.6 dB (typical)

100–20000 MHz; Insertion loss 1.6 dB (typical); Isolation 45 dB (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz; TA = +25 °C

Insertion loss: Typical: 1.6; Unit: dB; TA = +25 °C

Isolation: Typical: 45; Unit: dB; TA = +25 °C

Negative-supply quiescent current: Typical: 0.0012; Unit: A

Product details Product datasheet



LCI-SW-8000-12000-SPDT

8000–12000 MHz GaN SPDT MMIC Switch Die — IL 0.9 dB (typical)

8000–12000 MHz; Insertion loss 0.9 dB (typical); Isolation 45 dB (typical); P0.2dB 46 dBm (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

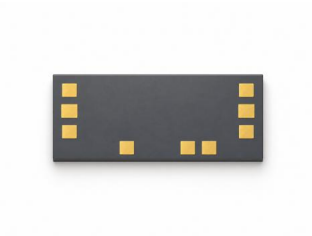
Insertion loss: Typical: 0.9; Unit: dB

Isolation: Typical: 45; Maximum: 50; Unit: dB

Input power at 0.2 dB compression: Typical: 46; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SPST-D

100–20000 MHz GaAs SPST MMIC Switch Die — IL ≤ 1.2 dB

100–20000 MHz; Insertion loss ≤ 1.2 dB; Isolation 60 dB (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz

Insertion loss: Maximum: 1.2; Unit: dB

Isolation: Typical: 60; Unit: dB

Input/output VSWR (on): Typical: 1.1

TA = +25 °C

Product details Product datasheet



LCI-SW-2700-3500-SPDT

2700–3500 MHz GaN SPDT MMIC Switch Die — IL 0.7 dB (typical)

2700–3500 MHz; Insertion loss 0.7 dB (typical); Isolation 41 dB (typical); P0.2dB 51 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

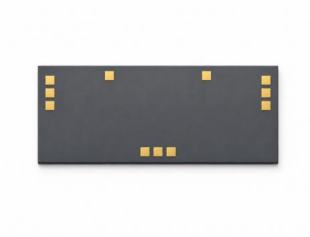
Insertion loss: Typical: 0.7; Unit: dB

Isolation: Typical: 41; Maximum: 43; Unit: dB

Input power at 0.2 dB compression: Typical: 51; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-SW-100-6000-SPDT

100–6000 MHz GaN SPDT MMIC Switch Die — IL 0.7 dB (typical)

100–6000 MHz; Insertion loss 0.7 dB (typical); Isolation 45 dB (typical); P0.2dB 47 dBm (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 6000; Value: 100–6000; Unit: MHz

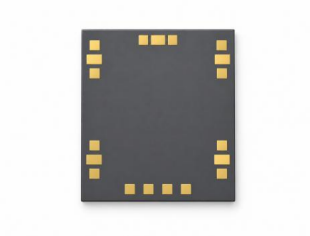
Insertion loss: Typical: 0.7; Maximum: 0.8; Unit: dB

Isolation: Typical: 45; Unit: dB

Input power at 0.2 dB compression: Typical: 47; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SP4T-D

100–20000 MHz GaAs SP4T MMIC Switch Die — IL −2 dB (typical)

100–20000 MHz; Insertion loss -2 dB (typical); Isolation -50 dB (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz

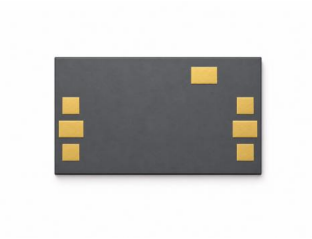
Insertion loss: Typical: -2; Unit: dB

Isolation: Typical: -50; Unit: dB

Input VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCI-AMP-8000-12000-P1DB16T

8000–12000 MHz GaAs MMIC Amplifier Die — P1dB 16 dBm (typical)

8000–12000 MHz; P1dB 16 dBm (typical); Small-signal gain 24 dB (typical); NF 1.7 dB (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

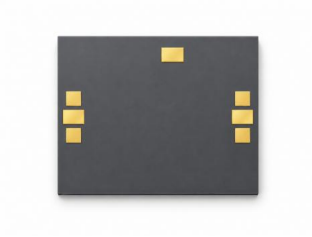
Output 1 dB compression power: Symbol: P1dB; Typical: 16; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 24; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-700-5000-P1DB19T

700–5000 MHz GaAs MMIC Amplifier Die — P1dB 19 dBm (typical)

700–5000 MHz; P1dB 19 dBm (typical); Small-signal gain 14 dB (typical); NF 2.5 dB (typical).

Operating frequency: Symbol: f; Minimum: 700; Maximum: 5000; Value: 700–5000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 19; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 14; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-2700-3500-P1DB23p5T

2700–3500 MHz GaAs MMIC Amplifier Die — P1dB 23.5 dBm (typical)

2700–3500 MHz; P1dB 23.5 dBm (typical); Small-signal gain 28 dB (typical); NF 3.5 dB (typical).

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

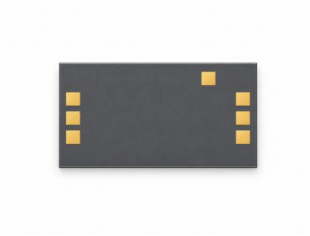
Output 1 dB compression power: Symbol: P1dB; Typical: 23.5; Unit: dBm

Saturated output power: Symbol: Psat; Value: 25; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 28; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-14000-18000-P1DB23T-D

14000–18000 MHz GaAs MMIC Amplifier Die — P1dB 23 dBm (typical)

14000–18000 MHz; P1dB 23 dBm (typical); Small-signal gain 19 dB (typical); NF 5.5 dB (typical).

Operating frequency: Symbol: f; Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

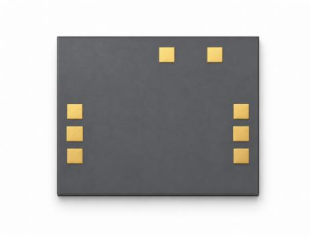
Output 1 dB compression power: Symbol: P1dB; Typical: 23; Unit: dBm

Saturated output power: Symbol: Psat; Value: 24; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 19; Maximum: 23; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-5000-20000-P1DB20T

5000–20000 MHz GaAs MMIC Amplifier Die — P1dB 20 dBm (typical)

5000–20000 MHz; P1dB 20 dBm (typical); Small-signal gain 21 dB (typical); NF 6.5 dB (typical).

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 20000; Value: 5000–20000; Unit: MHz

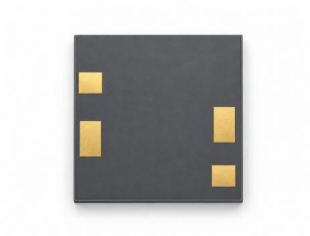
Output 1 dB compression power: Symbol: P1dB; Typical: 20; Unit: dBm

Saturated output power: Symbol: Psat; Value: 21; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 21; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-DC-6000-P1DB22p8T

DC–6000 MHz GaAs MMIC Amplifier Die — P1dB 22.8 dBm (typical)

DC–6000 MHz; P1dB 22.8 dBm (typical); Small-signal gain 21 dB (typical); NF 1.8 dB (typical).

Operating frequency: Symbol: f; Minimum: DC; Maximum: 6000; Value: DC–6000; Unit: MHz

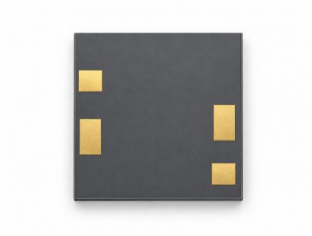
Output 1 dB compression power: Symbol: P1dB; Typical: 22.8; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 21; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-DC-6000-P1DB21T

DC–6000 MHz GaAs MMIC Amplifier Die — P1dB 21 dBm (typical)

DC–6000 MHz; P1dB 21 dBm (typical); Small-signal gain 20 dB (typical); NF 1 dB (typical).

Operating frequency: Symbol: f; Minimum: DC; Maximum: 6000; Value: DC–6000; Unit: MHz

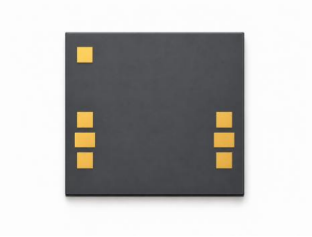
Output 1 dB compression power: Symbol: P1dB; Typical: 21; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 20; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-800-2000-P1DB15T

800–2000 MHz GaAs MMIC Amplifier Die — P1dB 15 dBm (typical)

800–2000 MHz; P1dB 15 dBm (typical); Small-signal gain 17 dB (typical); NF 1.4 dB (typical).

Operating frequency: Symbol: f; Minimum: 800; Maximum: 2000; Value: 800–2000; Unit: MHz

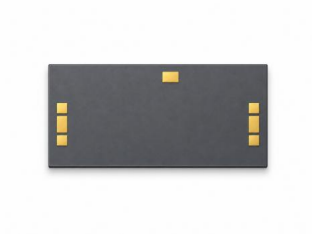
Output 1 dB compression power: Symbol: P1dB; Typical: 15; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 17; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-2000-7000-P1DB23p5T

2000–7000 MHz GaAs MMIC Amplifier Die — P1dB 23.5 dBm (typical)

2000–7000 MHz; P1dB 23.5 dBm (typical); Small-signal gain 21 dB (typical); NF 5 dB (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 7000; Value: 2000–7000; Unit: MHz

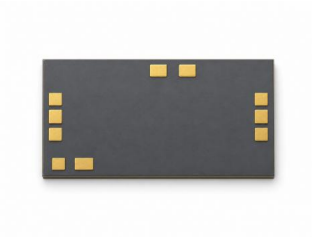
Output 1 dB compression power: Symbol: P1dB; Typical: 23.5; Unit: dBm

Saturated output power: Symbol: Psat; Value: 24.5; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 21; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-8000-12000-PS28T

8000–12000 MHz GaAs MMIC Amplifier Die — PSAT 28 dBm (typical)

8000–12000 MHz; PSAT 28 dBm (typical); Small-signal gain 21 dB (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

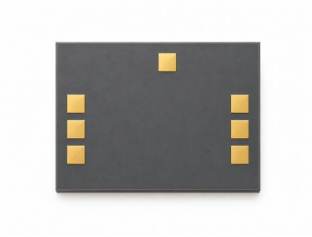
Saturated output power: Minimum: 27.8; Typical: 28; Unit: dBm

Power gain: Typical: 19; Unit: dB

Power-added efficiency: Typical: 40; Unit: %

TA = +25 °C; Vd = +5 V; Vg = -0.6 V

Product details Product datasheet



LCI-AMP-4000-9000-P1DB17T

4000–9000 MHz GaAs MMIC Amplifier Die — P1dB 17 dBm (typical)

4000–9000 MHz; P1dB 17 dBm (typical); Small-signal gain 13 dB (typical); NF 3.5 dB (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 9000; Value: 4000–9000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 17; Unit: dBm

Saturated output power: Symbol: Psat; Value: 18; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 13; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-2000-18000-P1DB16T

2000–18000 MHz GaAs MMIC Amplifier Die — P1dB 16 dBm (typical)

2000–18000 MHz; P1dB 16 dBm (typical); Small-signal gain 21 dB (typical); NF 3 dB (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 18000; Value: 2000–18000; Unit: MHz

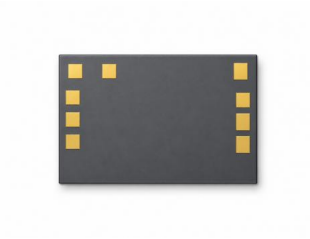
Output 1 dB compression power: Symbol: P1dB; Typical: 16; Unit: dBm

Saturated output power: Symbol: Psat; Value: 17; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 21; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-6000-12000-P1DB23T

6000–12000 MHz GaAs MMIC Amplifier Die — P1dB 23 dBm (typical)

6000–12000 MHz; P1dB 23 dBm (typical); Small-signal gain 23 dB (typical); NF 5 dB (typical).

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 12000; Value: 6000–12000; Unit: MHz

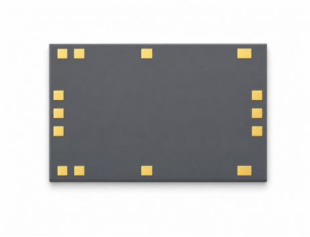
Output 1 dB compression power: Symbol: P1dB; Typical: 23; Unit: dBm

Saturated output power: Symbol: Psat; Value: 23.8; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 23; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-24000-31000-PS25T

24000–31000 MHz GaAs MMIC Amplifier Die — PSAT 25 dBm (typical)

24000–31000 MHz; PSAT 25 dBm (typical); Small-signal gain 22 dB (typical).

Operating frequency: Symbol: f; Minimum: 24000; Maximum: 31000; Value: 24000–31000; Unit: MHz

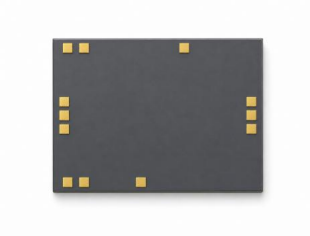
Small-signal gain: Typical: 22; Unit: dB

Saturated output power: Typical: 25; Unit: dBm

Power gain: Typical: 20; Unit: dB

TA = +25 °C; Vd = +5 V; Id = 160 mA

Product details Product datasheet



LCI-BDA-8000-18000-RXP1DB24T

8000–18000 MHz GaAs MMIC Bidirectional Amplifier Die — Rx / Tx P1dB 24 dBm (typical)

8000–18000 MHz; Rx / Tx: Rx / Tx P1dB 24 dBm (typical); Small-signal gain 21 dB (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 18000; Value: 8000–18000; Unit: MHz

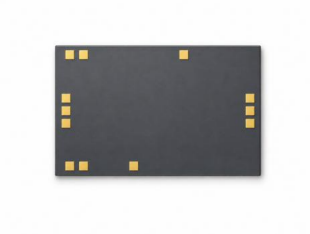
Output 1 dB compression power (Rx): Typical: 24; Unit: dBm

Saturated output power (Rx): Typical: 24.5; Unit: dBm

Small-signal gain (Rx): Typical: 21; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-BDA-6000-18000-RXP1DB21T

6000–18000 MHz GaAs MMIC Bidirectional Amplifier Die — Rx / Tx P1dB 21 dBm (typical)

6000–18000 MHz; Rx / Tx: Rx / Tx P1dB 21 dBm (typical); Small-signal gain 19 dB (typical).

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Value: 6000–18000; Unit: MHz

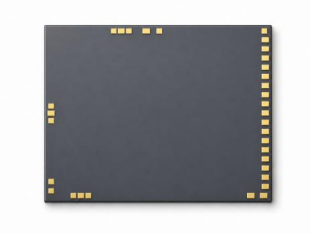
Output 1 dB compression power (Rx): Typical: 21; Unit: dBm

Saturated output power (Rx): Typical: 22; Unit: dBm

Small-signal gain (Rx): Typical: 19; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-APC-5000-6000

5000–6000 MHz GaAs MMIC Amplitude and Phase Control RF Front-End Die — Rx 13 dB / Tx 27 dB (typical)

5000–6000 MHz; Rx 13 dB / Tx 27 dB (typical); Rx P1dB ≥ 10 dBm; Tx PSAT ≥ 23 dBm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

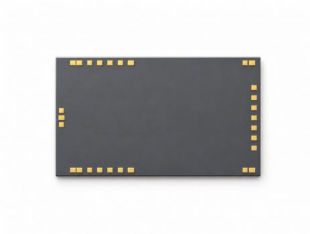
Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

Attenuation range: Minimum: 0.5; Maximum: 31.5; Unit: dB

Small-signal gain (Rx): Typical: 13; Unit: dB

TA = +25 °C; VS = -5 V; Vd1 = Vd2 = +5 V

Product details Product datasheet



LCI-BF-3700-5000-2CH

3700–5000 MHz Dual-Channel GaAs MMIC Phase and Attenuation Control Die — 2 × 6-bit ϕ / 6-bit ATT

3700–5000 MHz; Insertion loss -13 dB (typical); 64-state RMS attenuation error 0.2 dB (typical); 64-state RMS phase error 2 ° (typical).

Operating frequency: Symbol: f; Minimum: 3700; Maximum: 5000; Value: 3700–5000; Unit: MHz

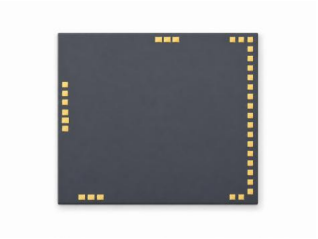
Insertion loss: Typical: -13; Unit: dB

Attenuation range: Maximum: 31.5; Unit: dB

64-state RMS attenuation error: Typical: 0.2; Unit: dB

TA = +25 °C; VEE = -5 V; Vd = +5 V

Product details Product datasheet



LCI-APC-8000-12000-D-RXG10T

8000–12000 MHz GaAs MMIC Amplitude and Phase Control RF Front-End Die — Rx 10 dB / Tx 26 dB (typical)

8000–12000 MHz; Rx 10 dB / Tx 26 dB (typical); Rx P1dB ≥ 13.5 dBm; Tx PSAT ≥ 25 dBm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

Attenuation range: Minimum: 0.5; Maximum: 31.5; Unit: dB

Small-signal gain (Rx): Typical: 10; Unit: dB

TA = +25 °C; VS = -5 V; Vd1 = Vd2 = +5 V

Product details Product datasheet



LCBPF-17000-19000

17000–19000 MHz GaAs Bandpass Filter Die — IL 2.7 dB (typical)

17000–19000 MHz; Insertion loss 2.7 dB (typical).

Operating frequency: Symbol: f; Minimum: 17000; Maximum: 19000; Value: 17000–19000; Unit: MHz

Center frequency: Typical: 18000; Unit: MHz

Insertion loss: Typical: 2.7; Unit: dB

Passband ripple: Typical: 0.5; Unit: dB

TA = +25 °C

Product details Product datasheet

Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.